

超低エネルギー・アナログ・RF回路技術 と新規分野への展開



An ultra-low energy analog and RF circuit technology for emerging applications

Akira Matsuzawa

**Dept. of Physical Electronics
Graduate School of Science and Engineering**

Lab. members

Professor: Akira Matsuzawa

Founded in 2004

Assoc. Prof.: Kenichi Okada (RF)

Assist. Prof.: Masaya Miyahara (ADC/DAC)

2 technical staff, 3 secretaries

14 doctor students (3 from corp.)

20 master students

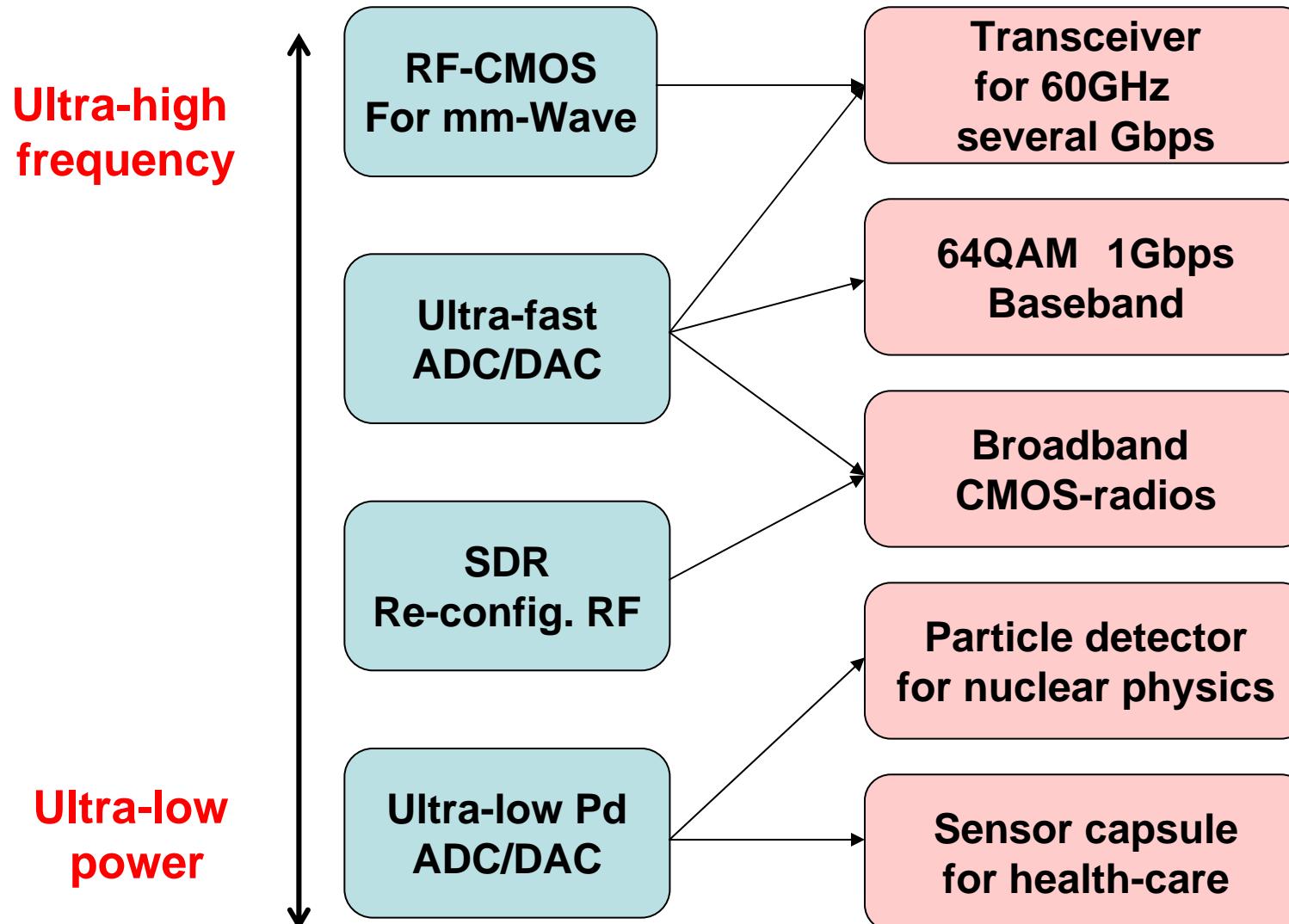
6 undergraduate students

some researchers from corp. **~50 people**

20 Japanese students and 20 foreign students

Focus of Laboratory

Core circuit tech. Applied LSIs and systems



We now developing SoCs for mm-wave systems

1. Long range: 4km
Fixed point
: 38GHz, 0.6—1.0 Gbps

with JRC and NEC



2. Short range: a few meter
: 60GHz, 3-10 Gbps

with Sony



Long range mm-wave: Fixed point 38GHz,1Gbps 4

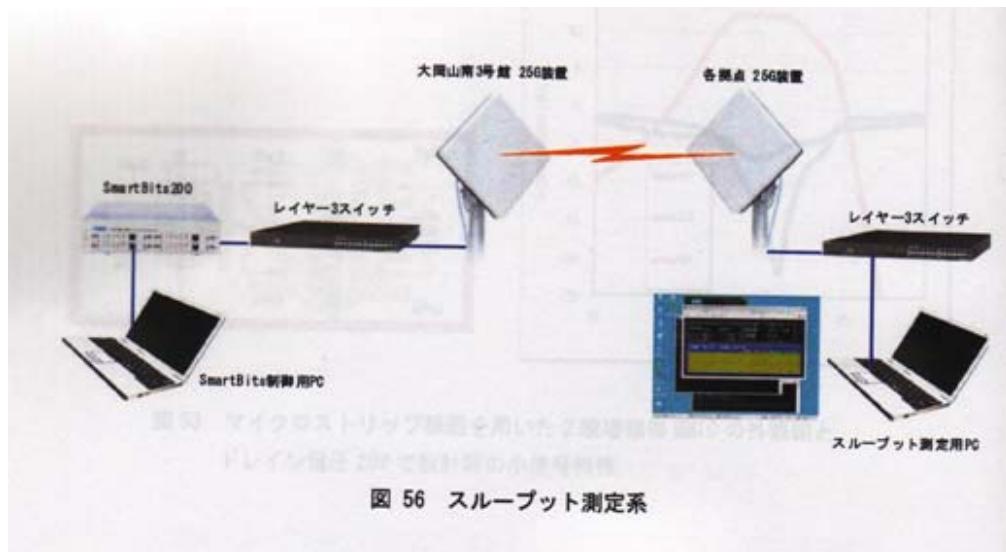


図 56 スループット測定系

Campus mm wave network



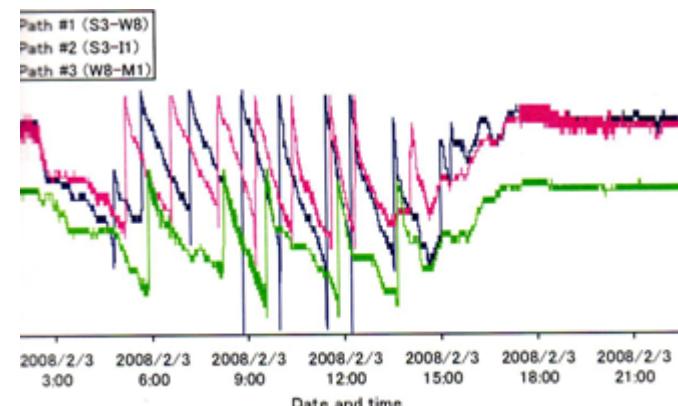
2009/11/30

Tokyo Tech



Equipment with plane Antenna

Networks durability against rain



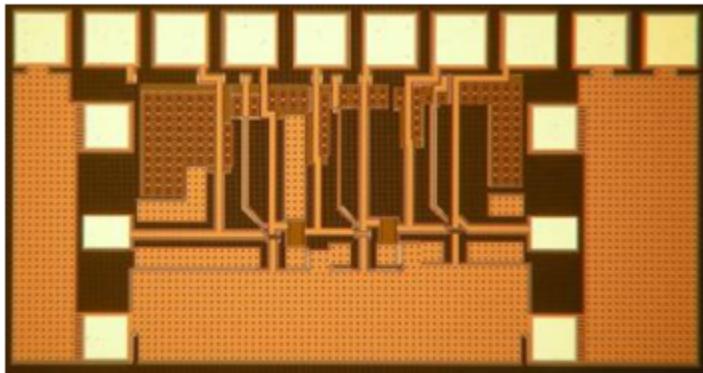
(e) 2008年2月3日 (雪。3センチほど積もる)

Developing 60GHz mm-wave circuits

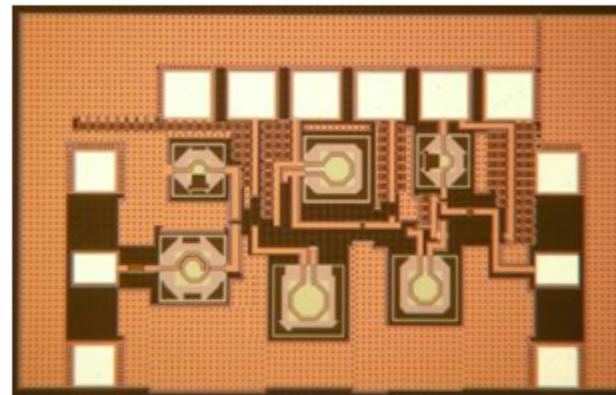
5

We now developing 60GHz CMOS Transceiver.

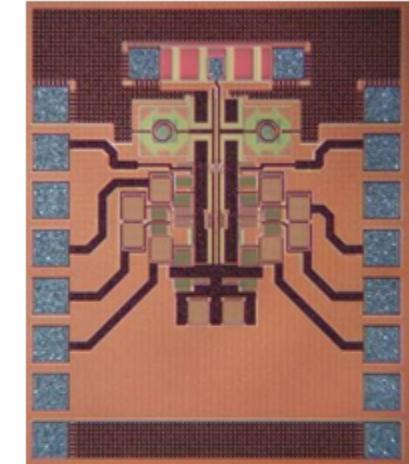
PA (90nm)



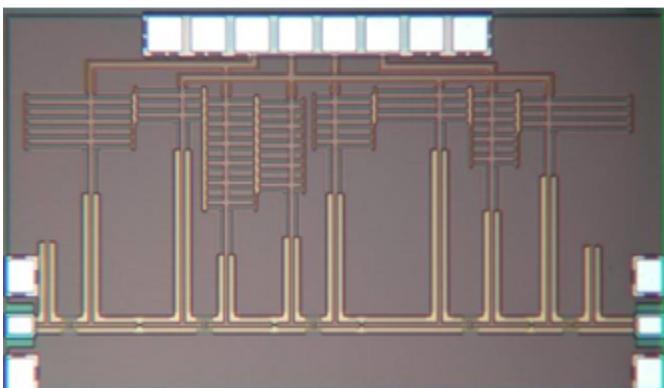
LNA (90nm)



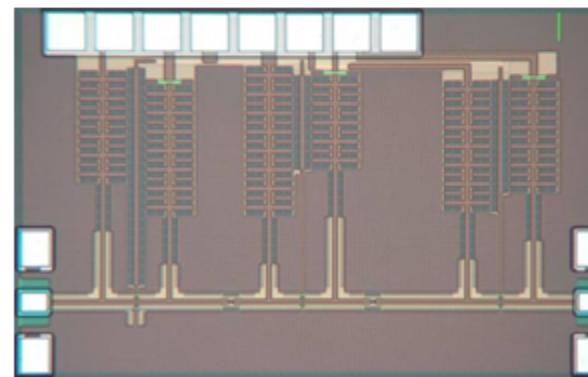
VCO (90nm)



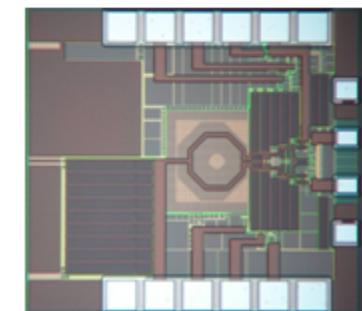
PA (65nm)



LNA (65nm)



VCO (65nm)



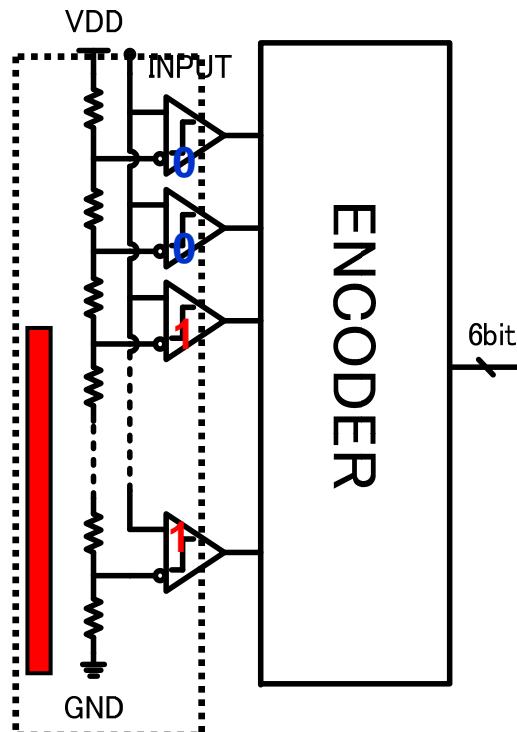
An ultra-low energy analog and RF circuit technology for emerging applications

Flash ADC architecture

- Expecting highest speed
- Comparator determines the ADC performance

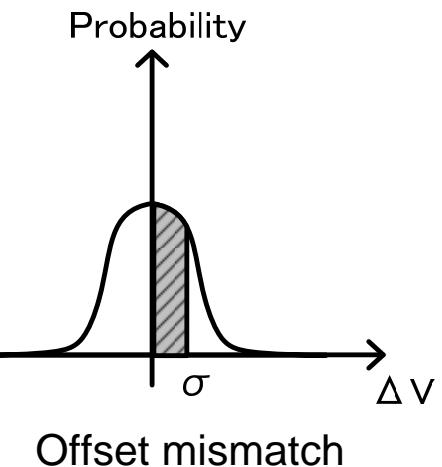
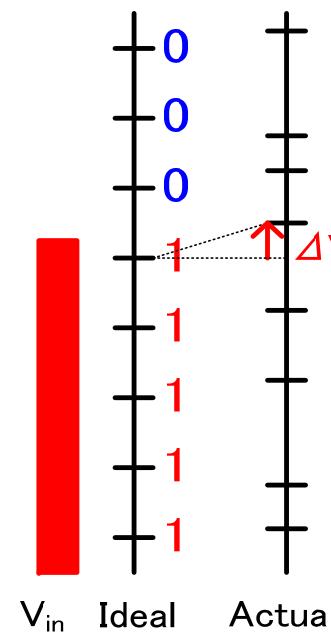
Low offset mismatch and noise are preferable

Flash ADC
Comparator
Array 6b: 63



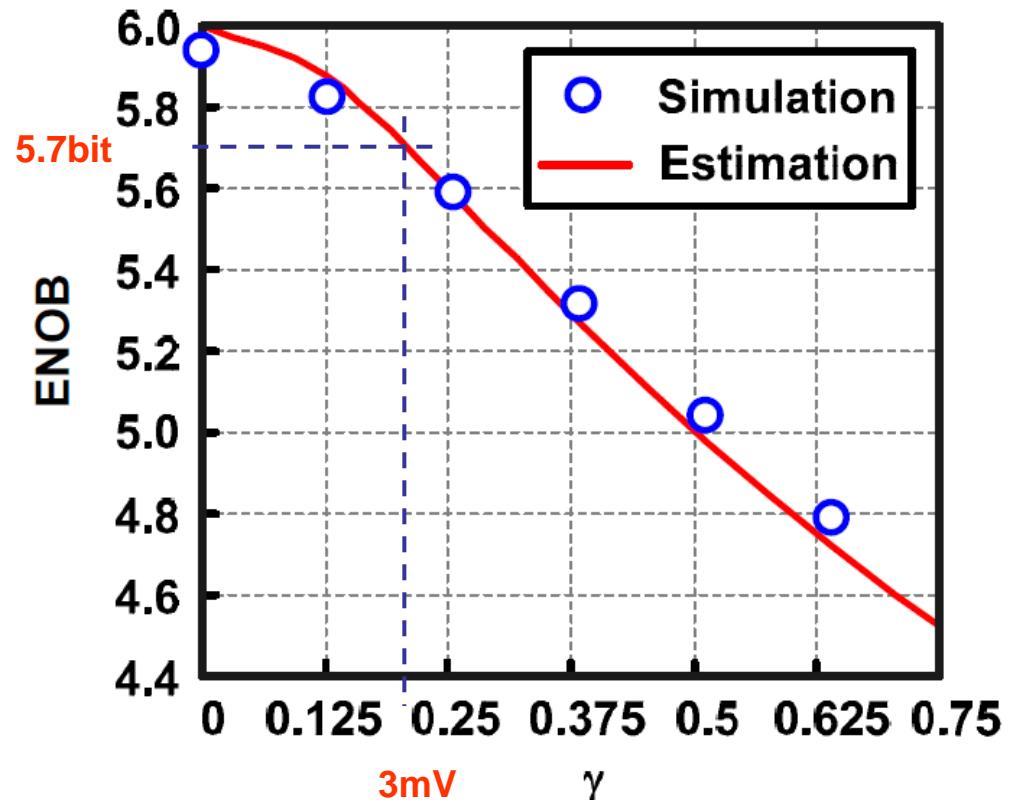
$$V_q = \frac{V_{FS}}{2^N}$$

$V_q = 16\text{mV}$, Mismatch $< 3\text{mV}$



Degradation of ENOB

Degradation of ENOB in flash ADC is basically determined by offset mismatch and thermal noise of comparators.



For example; 6bit ADC, ENOB=5.7bit
 $V_q=16\text{mV}$, $V_{off}<3\text{mV}$

$$\Delta ENOB = \frac{1}{2} \log_2 (1 + 12\gamma^2)$$

$$\gamma^2 = \left(\frac{V_{off}(\sigma)}{V_q} \right)^2 + \left(\frac{V_n(\sigma)}{V_q} \right)^2$$

$V_{off}(\sigma)$: Distribution of offset
 $V_n(\sigma)$: Distribution of noise

FoM of Flash ADC

FoM of flash ADC is determined by energy consumption of unit comparator and the degradation of effective bit.

Reduction of consumed energy and increase of ENOB are very important

$$FoM = \frac{P_d}{f_s \times 2^{ENOB}} \approx \frac{E_c \cdot f_s \cdot 2^N}{f_s \times 2^{N-\Delta ENOB}} = E_c \cdot 2^{\Delta ENOB}$$

E_c : Energy/Comparator

$$E_c = CV_{DD}^2$$

E_c is basically proportional to the capacitance

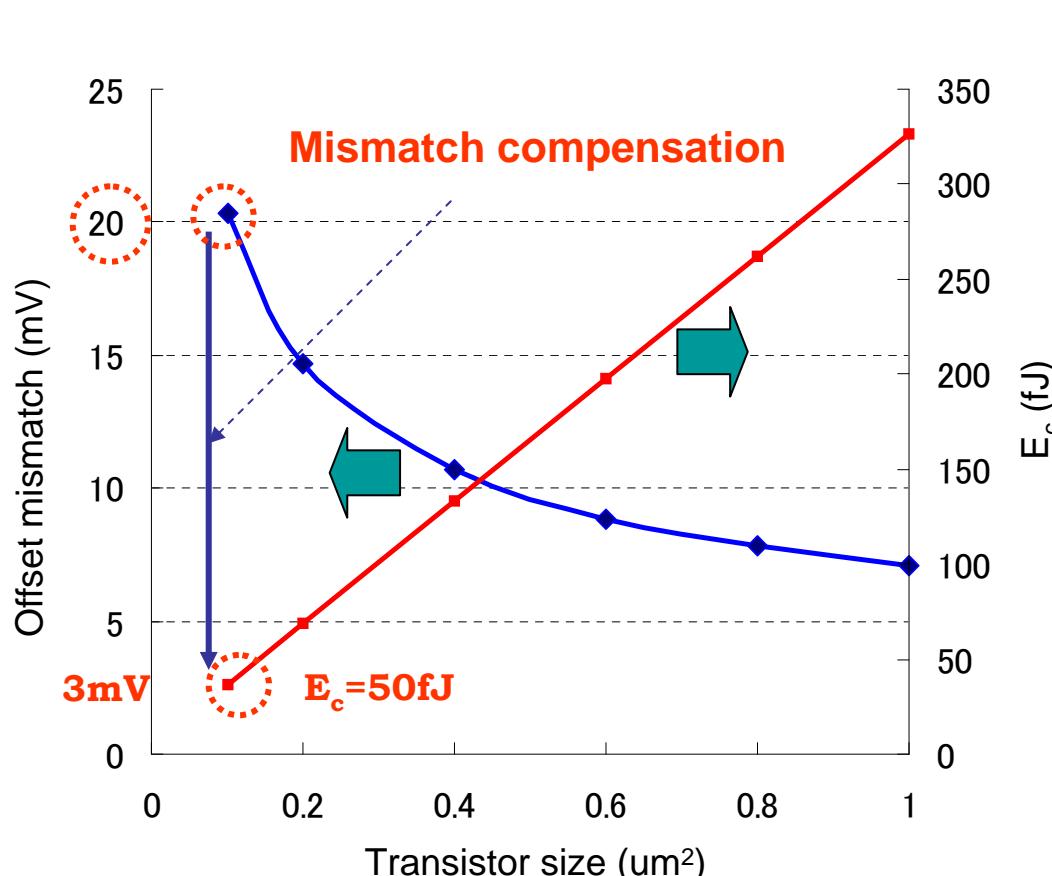
Tradeoff: mismatch and energy consumption

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There is a serious tradeoff between mismatch of transistor and gate area.

Larger transistor is required to reduce mismatch voltage and results in increase of gate area and consumed power.



Example

6bit ADC: $V_{\text{off}} < 3\text{mV}$
 $E_c < 50\text{fJ} \rightarrow 0.1\mu\text{m}^2 \rightarrow V_{\text{off}} = 20\text{mV}$
Needs mismatch compensation
 $20\text{mV} \rightarrow 3\text{mV}$

$$V_{\text{offset}}(\sigma) \propto \frac{1}{\sqrt{LW}}$$

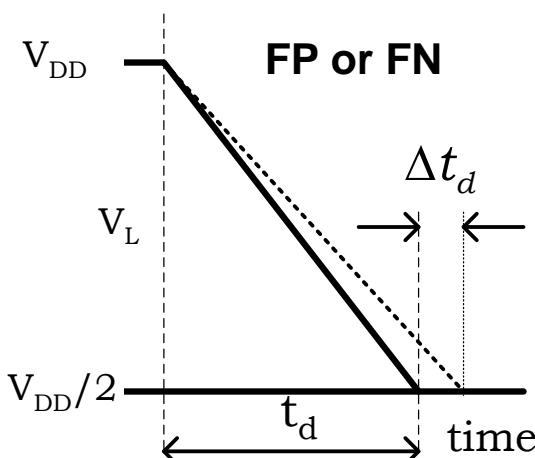
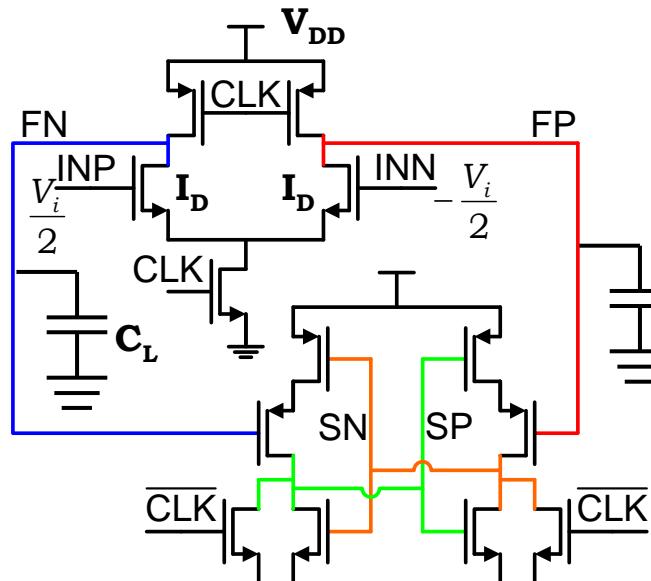
$$E_c \propto C_c \propto LW$$

$$E_c \propto \frac{1}{V_{\text{offset}}^2(\sigma)}$$

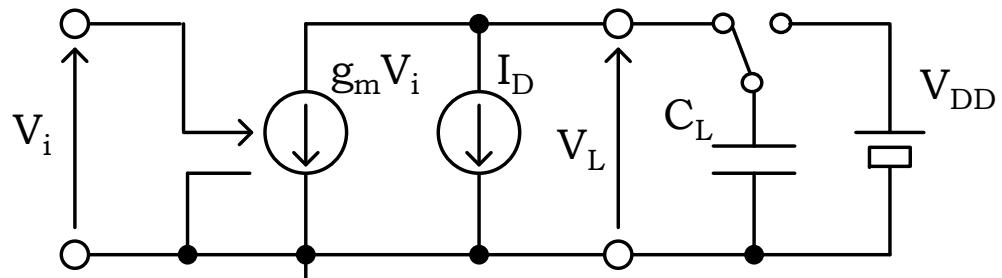
Mismatch compensation of dynamic comparator

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The mismatch can be compensated by capacitance and current.



Equivalent circuit of the first stage.



$$\text{Delay time } t_d = \frac{V_{DD} C_L}{2I_D}$$

$$I_D \propto (V_{gs} - V_T)^\alpha = V_{eff}^\alpha$$

$$g_m = \frac{dI_D}{V_{eff}} = \alpha \frac{I_D}{V_{eff}}$$

$$\frac{dt_d}{dV_i} = \frac{dt_d}{dI_D} \cdot \frac{dI_D}{dV_i} = -\frac{V_{DD} C_L}{2I_D} \frac{g_m}{I_D} = -t_d \frac{\alpha}{V_{eff}} \quad \therefore \frac{g_m}{I_D} = \frac{\alpha}{V_{eff}}$$

$$\therefore \frac{\Delta t_d}{t_d} = \alpha \frac{\Delta V_i}{V_{eff}} \quad \frac{\Delta t_d}{t_d} = \left(\frac{\Delta C_L}{C_L} - \frac{\Delta I_D}{I_D} \right)$$

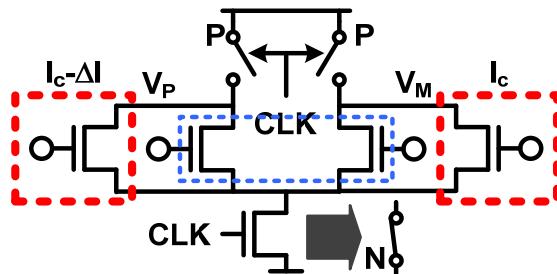
$$\therefore \frac{\Delta t_d}{t_d} = \alpha \frac{\Delta V_i}{V_{eff}}$$

$$\Delta V_i = \frac{V_{eff}}{\alpha} \left(\frac{\Delta C_L}{C_L} - \frac{\Delta I_D}{I_D} \right)$$

Digital calibration method

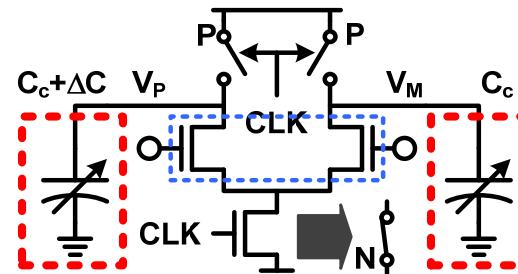
12

Resistor ladder type

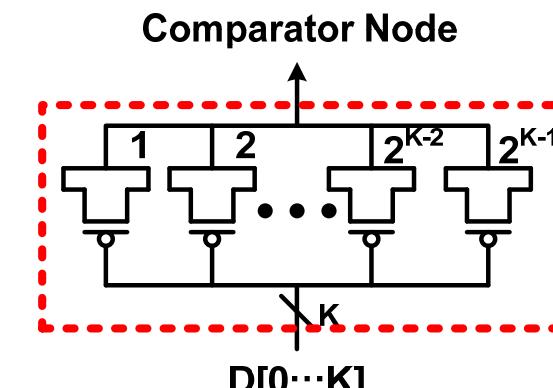
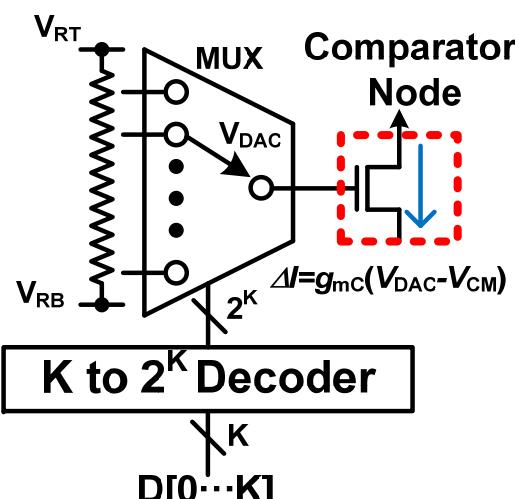


Current calibration

Capacitor array type



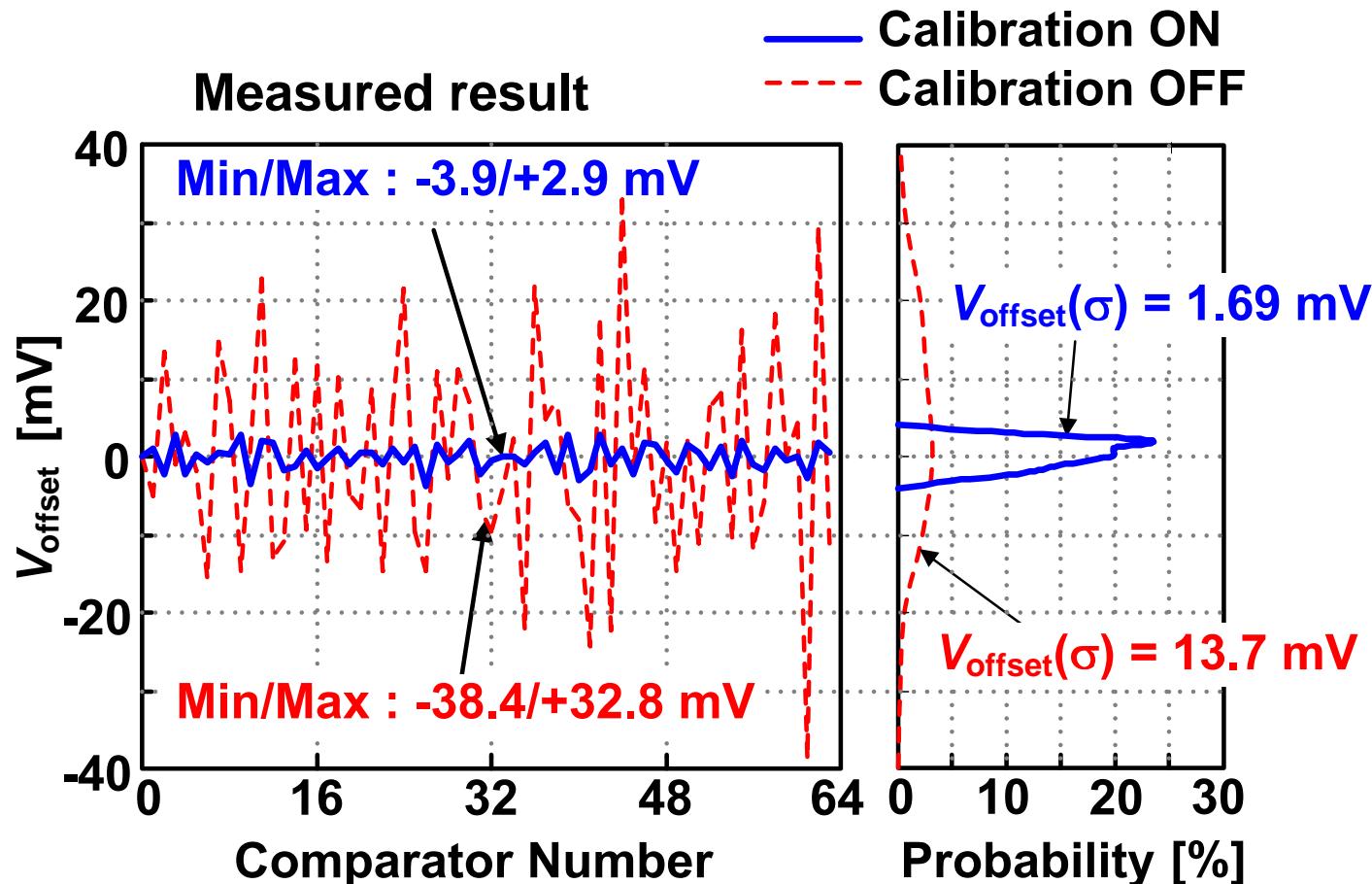
Capacitance calibration



Binary weighted capacitor array

Effect of analog mismatch compensation / 13

We can reduce the mismatch voltage from 14mV to 1.7mV at sigma.



M. Miyahara, Y. Asada, D. Paik, and A. Matsuzawa, "A Low-Noise Self-Calibrating Dynamic Comparator for High-Speed ADCs," A-SSCC, Nov. 2008.

Match with noise simulation

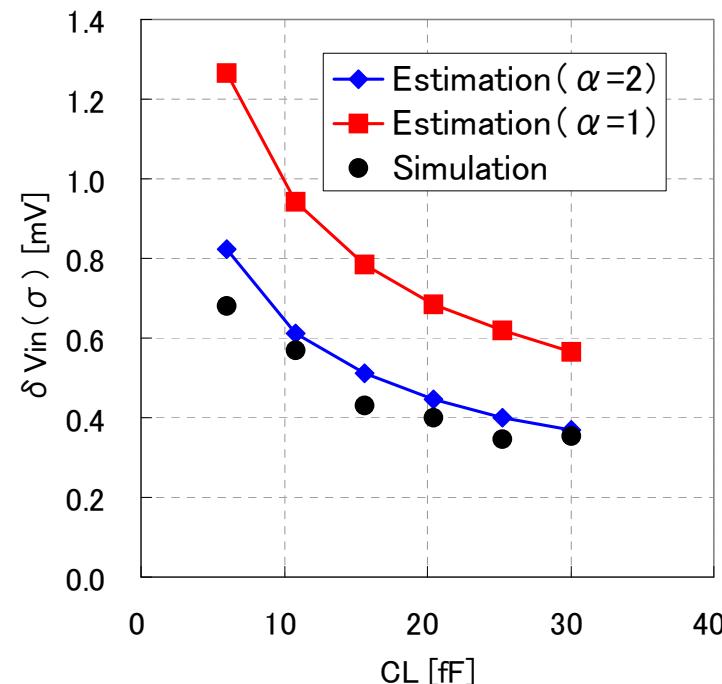
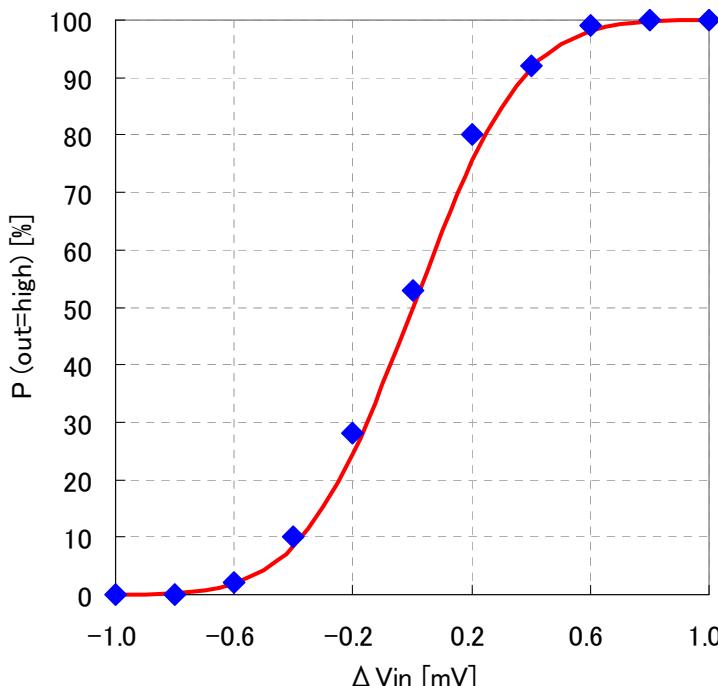
14

The deduced equation has a good match with simulation.

$$\delta V_{in} \approx 2 \sqrt{\frac{kTV_{eff}}{\alpha C_L V_{DD}}}$$

We deduced
this noise equation

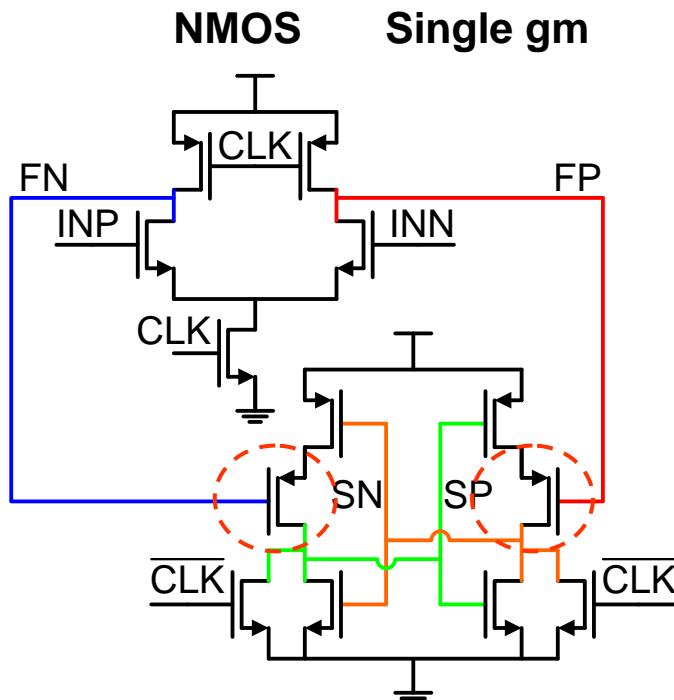
Noise in comparator



Comparison of comparators

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Double clock

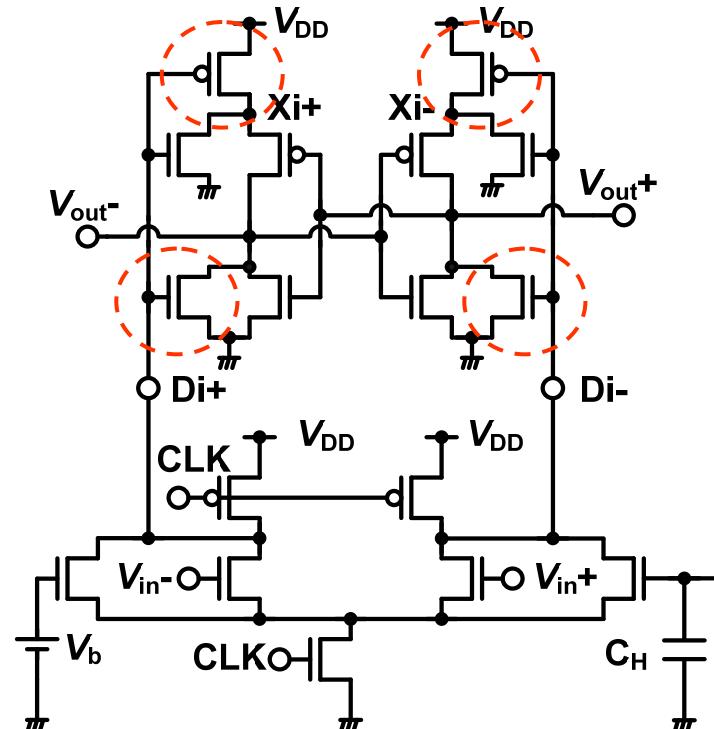


Conventional

M. van Elzakker, Ed van Tuijl, P. Geraedts, D. Schinkel, E. Klumperink, B. Nauta, "A 1.9uW 4.4fJ/Conversion-step 10b 1MS/s Charge-Redistribution ADC," IEEE ISSCC 2008, Dig. of Tech. Papers, pp.244-245, Feb. 2008.

Single clock

NMOS+PMOS Double gm



Our proposed

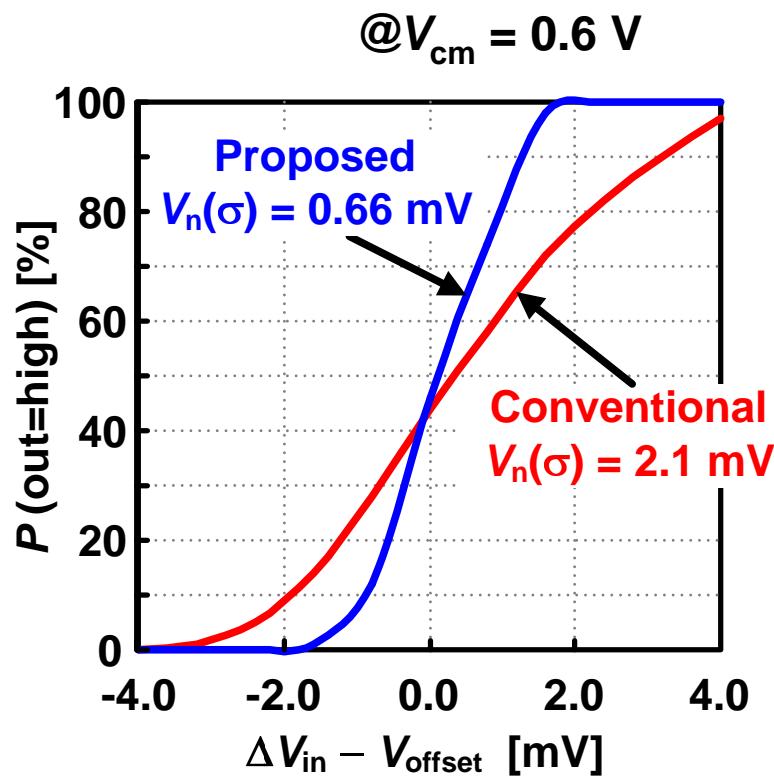
M. Miyahara, Y. Asada, D. Paik, and A. Matsuzawa, "A Low-Noise Self-Calibrating Dynamic Comparator for High-Speed ADCs," A-SSCC, Nov. 2008.

Noise reduction of comparator

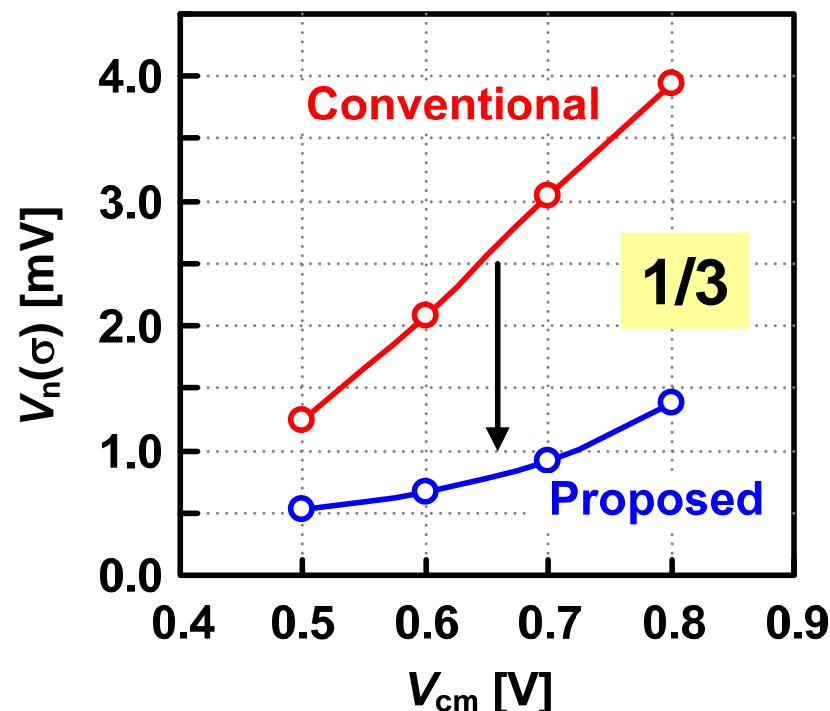
Proposed double-tail latch comparator can reduce noise down to 1/3.

$V_{DD} = 1.0 \text{ V}$, $F_C = 4 \text{ GHz}$, Transient-Noise simulations.

(Offset calibration is not used.)



M. Miyahara, Y. Asada, D. Paik, and A. Matsuzawa, "A Low-Noise Self-Calibrating Dynamic Comparator for High-Speed ADCs," A-SSCC, Nov. 2008.



Compensation of offset variation with good efficiency

A1. Double-tail latched comparator

A2. Digital calibration by capacitance adjusting

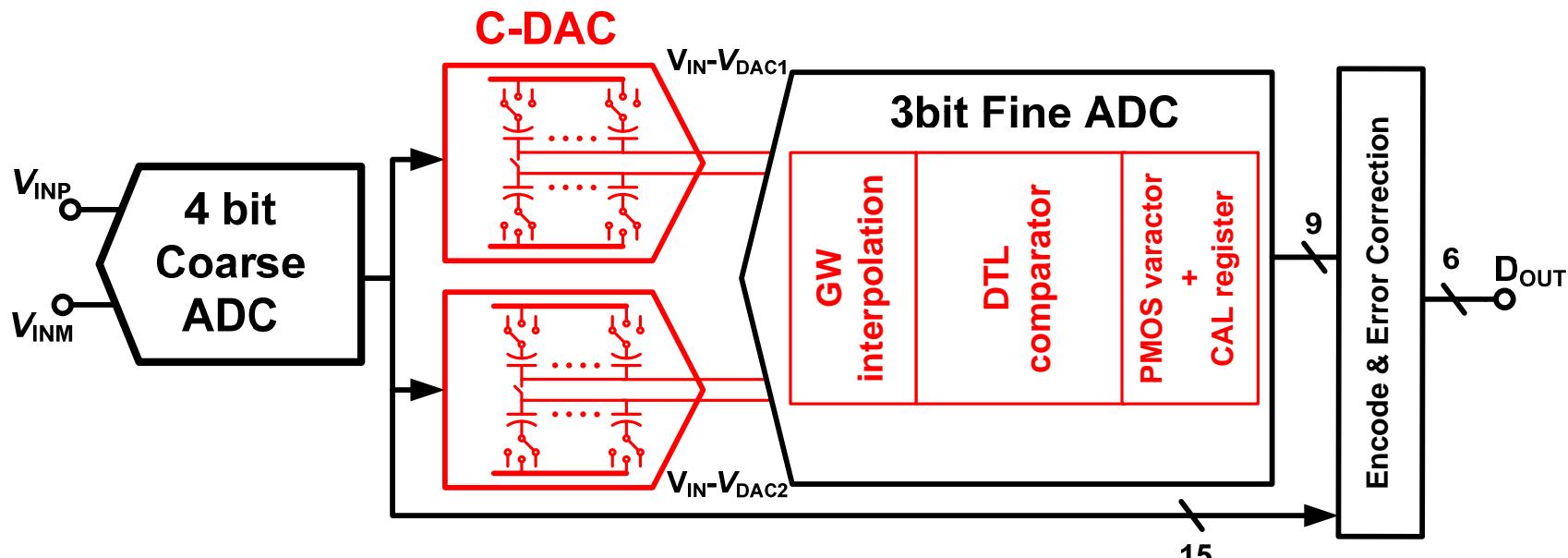
Reference voltage generation of sub-range

B1. Capacitive DAC (C-DAC)

B2. Gate-weighted interpolation

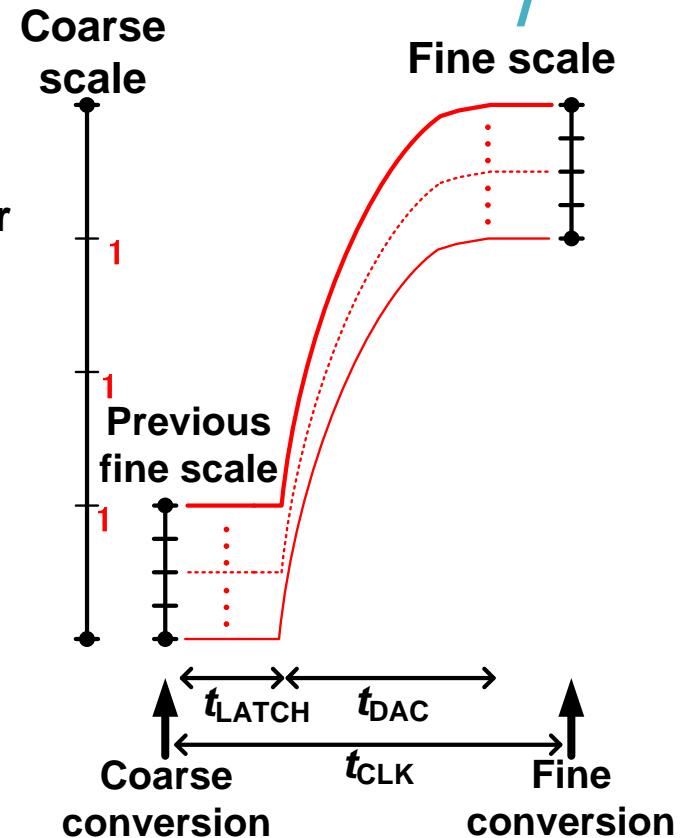
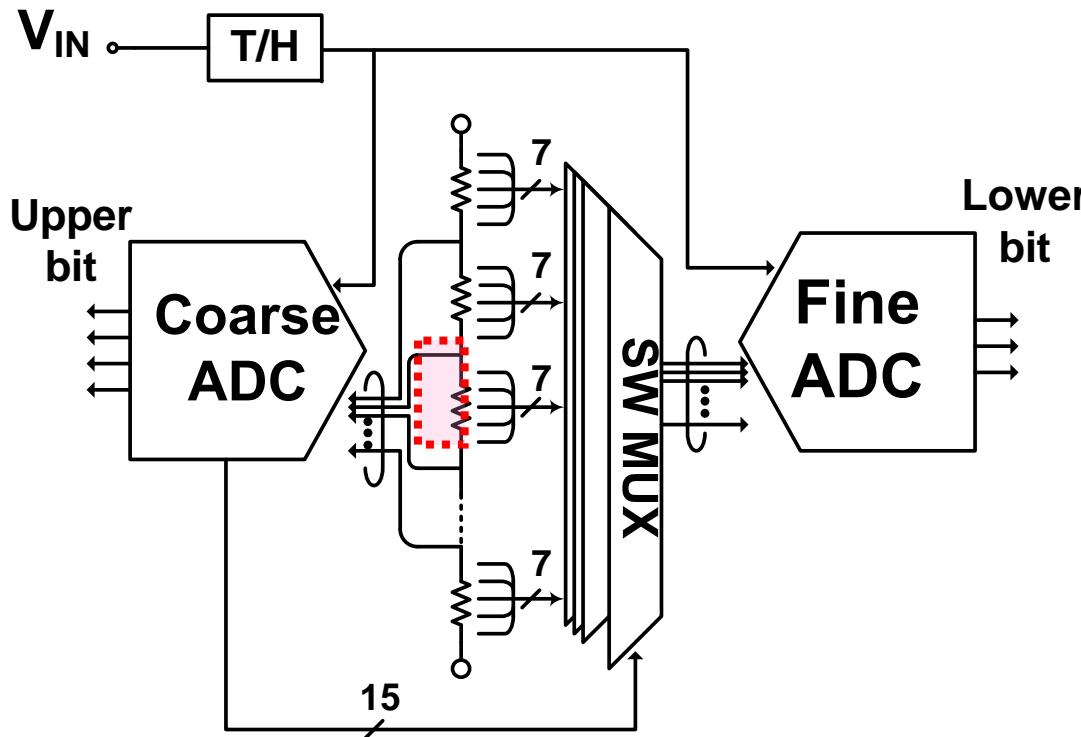
Y. Asada, K. Yoshihara, T. Urano, M. Miyahara and A. Matsuzawa,
“A 6bit, 7mW, 250fJ, 700MS/s Subranging ADC” A-SSCC, pp. 141-144, Nov. 2009.

→ Proposed circuits consume no static power.



Issue of reference voltage generation

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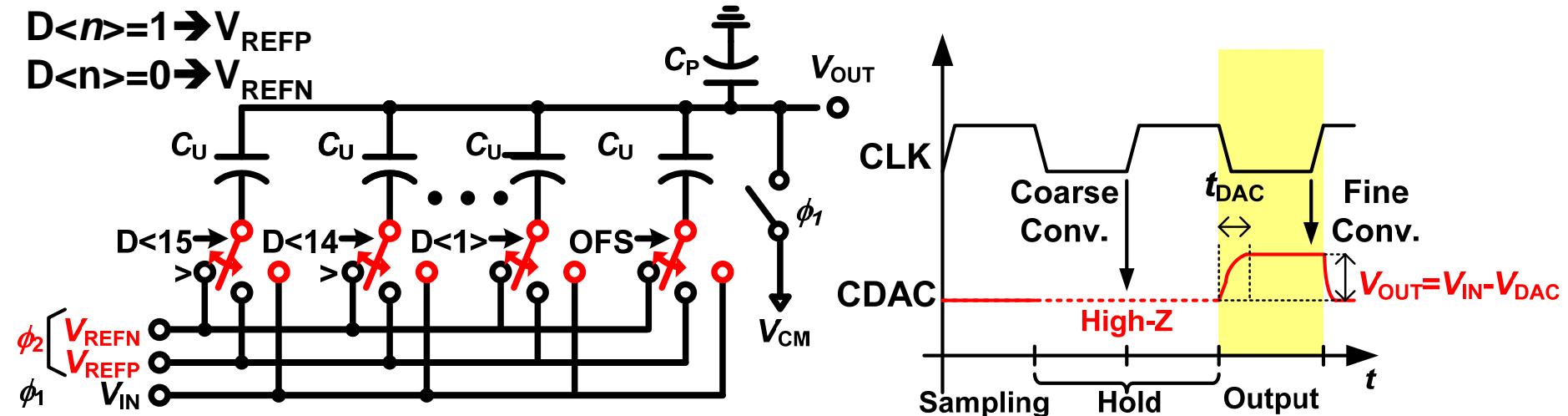


Resistor ladder + SW MUX:

- **Static power consumption** in resistor ladder
- Trade-off between **settling time** and **power consumption**
- **Many SW** for fine reference

→ Power consumption is inevitable with high speed operation.

CAD can realize fast operation with low Pd



Advantage :

- Operating as **S/H circuit**
- **No static power consumption** ($360\mu\text{W}@1\text{GHz}$)
- Smaller C_u realize **faster settling time**
($t_{DAC} = 3.4 r_{on} C_u < 80\text{ps}$ @ $r_{ON} = 1\text{k}\Omega$, $C_u = 15\text{fF}$)

Interpolation comparator

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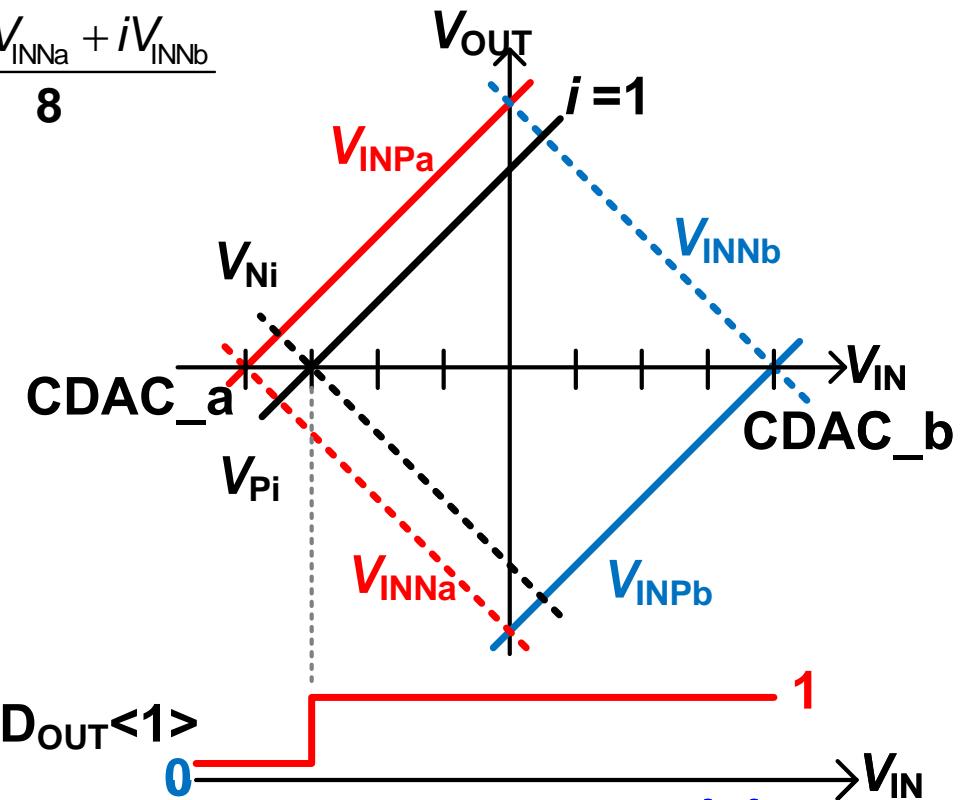
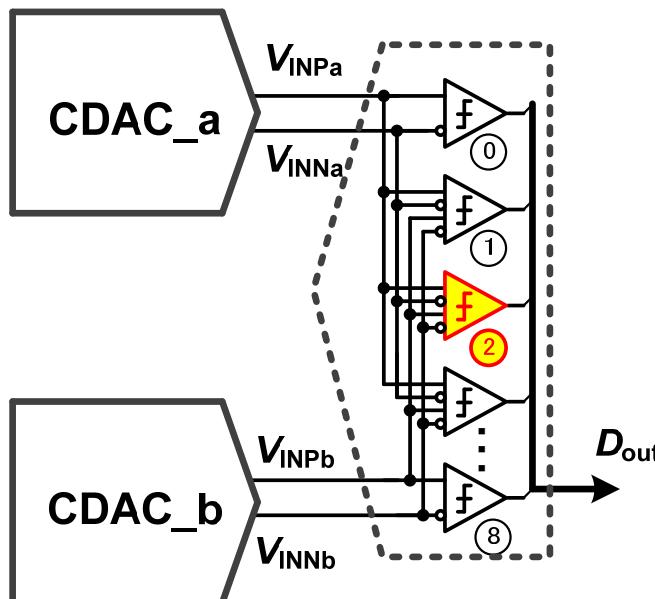
Interpolation can match upper and lower conversion ranges self-consistently.

FADC composed of interpolation comparator

Threshold voltage of i th comparator is **the cross-point of V_{Pi} , V_{Ni}** .

V_{Pi} , V_{Ni} : interpolated signal of CDAC outputs.

$$V_{Pi} = \frac{(8-i)V_{INPa} + iV_{INPb}}{8}, V_{Ni} = \frac{(8-i)V_{INNa} + iV_{INNb}}{8}$$

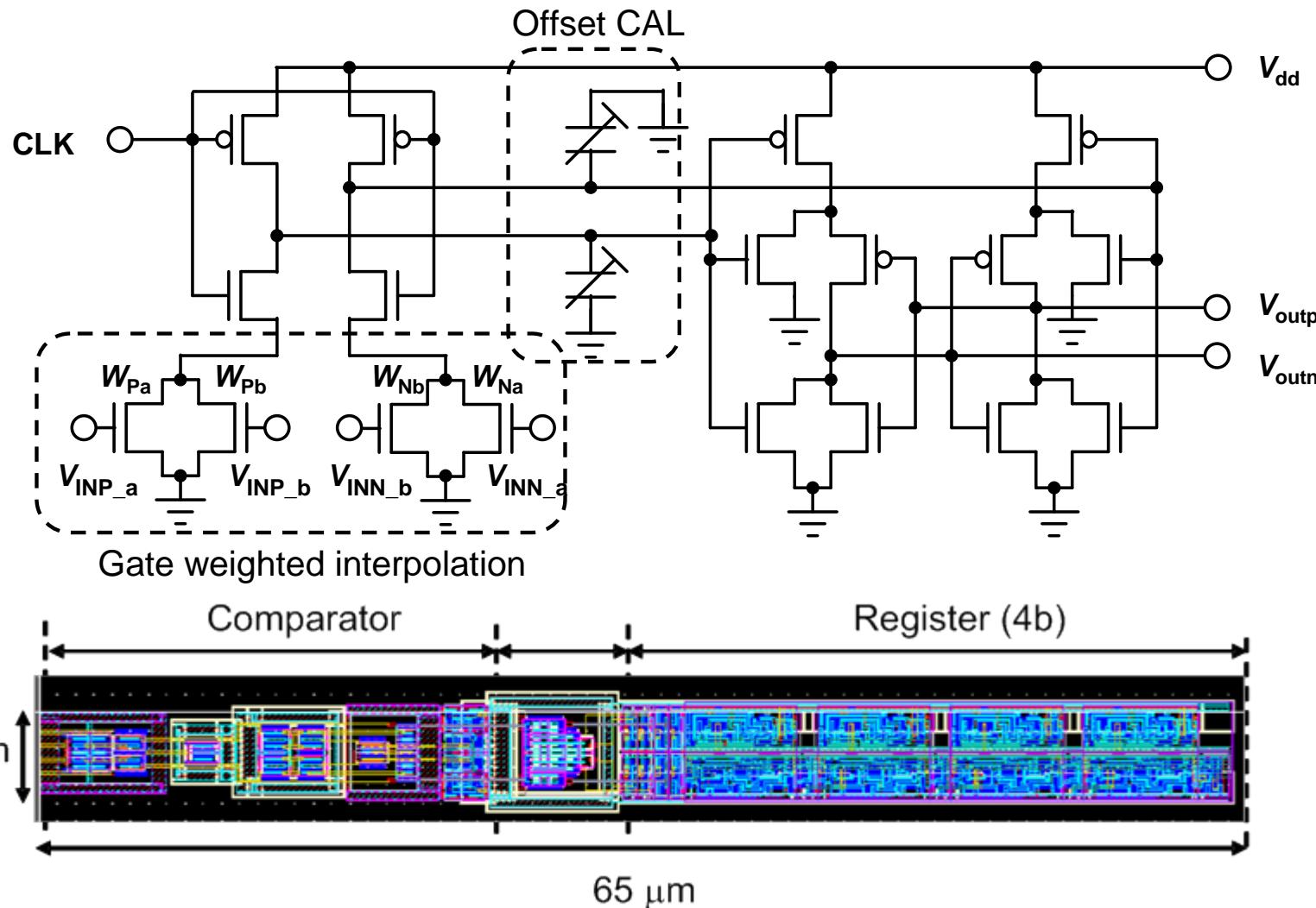


Comparator Circuits

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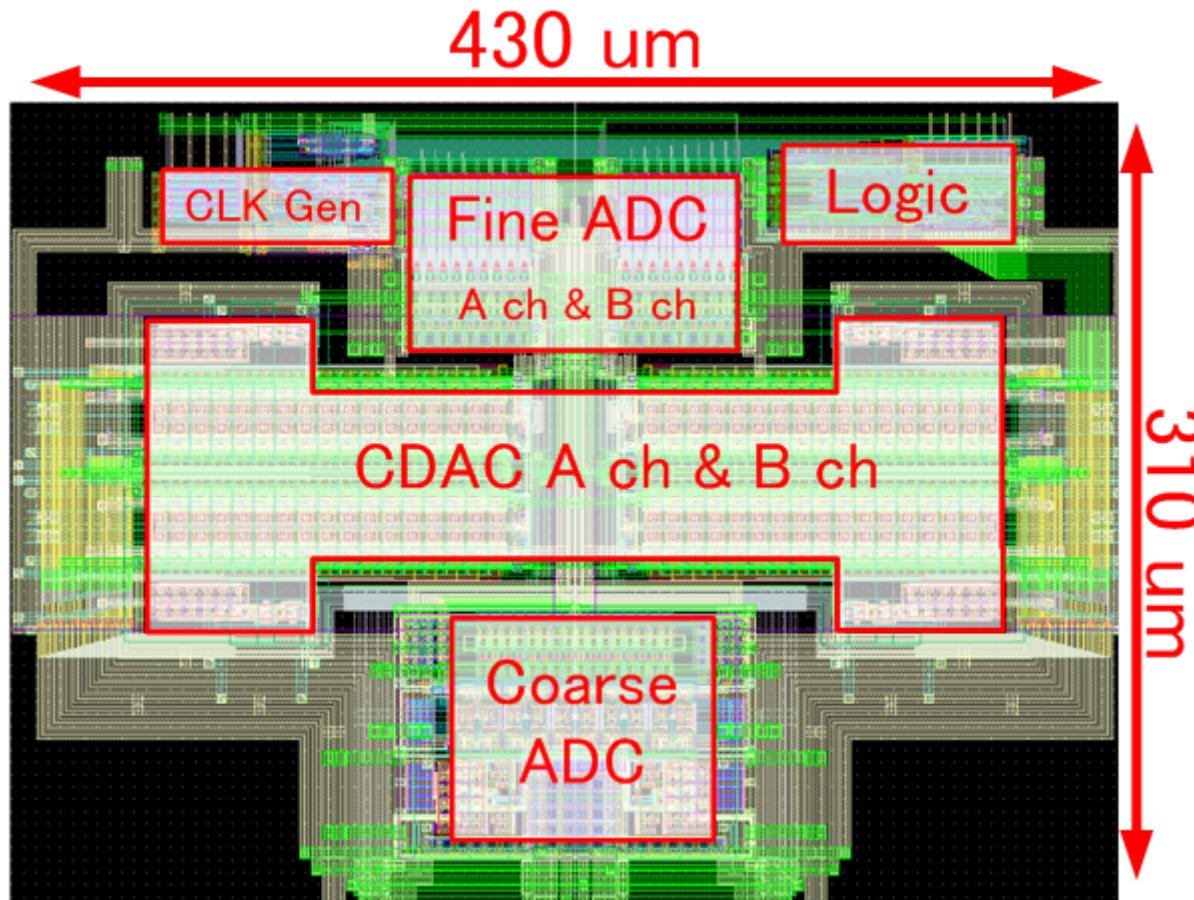
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Comparator with offset CAL realizes small area and high accuracy.



Chip photo & Layout

6 bit ADC has been realized in a 90 nm 10M1P CMOS technology with a chip area of 0.13mm²



Performance Summary

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World lowest FoM ADC!!

Proposed circuits has realized the best power efficiency.

	[1]	[2]	[3]	[4]	[6]	This Work
Resolution(bit)	6	6	6	6	6	6
fs(GS/s)	0.8	1.2	0.7	1.25	1	0.7
SNDR(DC/Nyq.)	35/32	34/33	31/30	34/28	35/33	35/34
Pd (mW)	12	75	24	32	30	7
Active area(mm ²)	0.13	0.43	0.052	0.09	0.18	0.13
VDD(V)	1.2	1.2	1.2	1.2	1.2/1.0	1.2
FoM(pJ)	0.44	2.17	1.31	1.22	0.8	0.25
CMOS Tech.(nm)	65	130	130	130	90	90
Architecture	Flash	Flash	Pipeline	2b-SAR	Subrange	Subrange

[1] C-Y. Chen, VLSI Circuits 2008.

[2] B-W. Chen, A-SSCC 2008.

[3] F. C. Hsieh, A-SSCC 2008.

[4] Z. Cao, ISSCC 2008.

[6] Y. C. Lien, A-SSCC 2008.

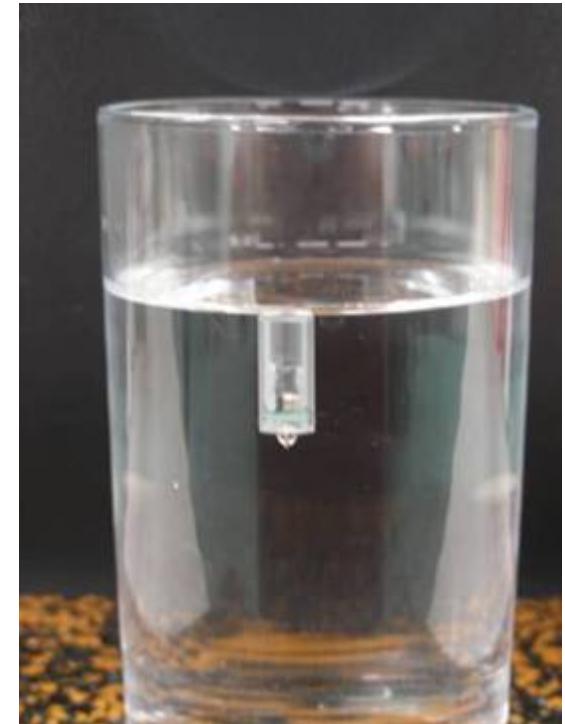
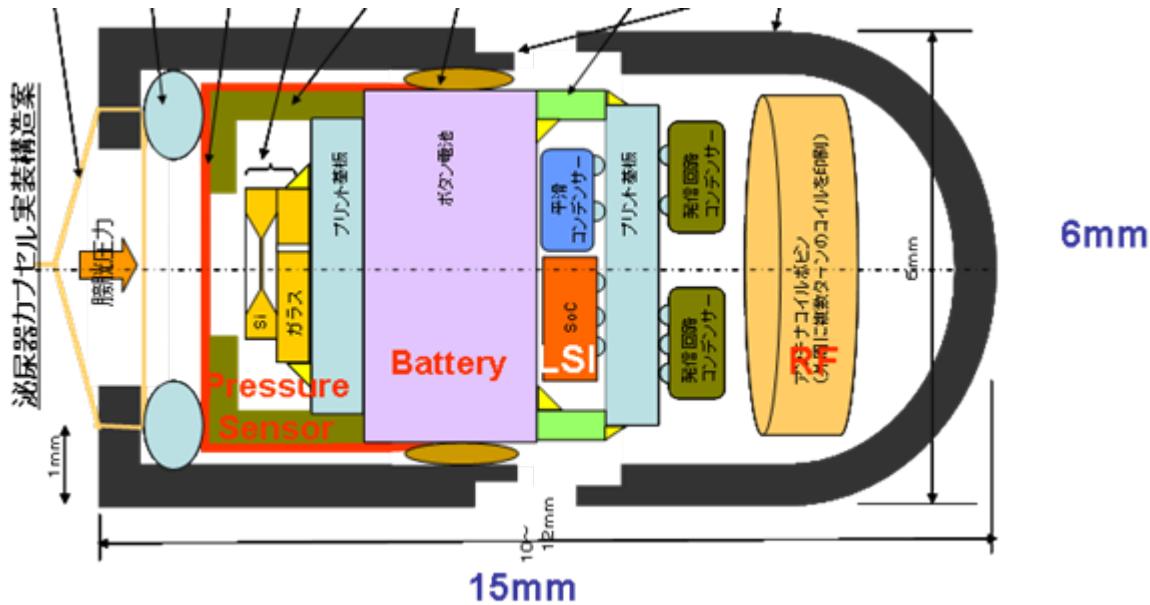
- **Micro medical systems**
 - Ultra-low power Capacitance to Digital converter
 - Can be applied to micro-sensor networks
 - Tire pressure sensor
- **Nuclear particle detector**
 - Pixels has an A/D converter in each
 - Can be applied to medical imaging devices
- **Full digital DC/DC converter**
 - Low power and high speed and resolution ADC
 - Every power supply systems
 - On-chip power supply

Capsule to measure bladder pressure

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Measure the bladder pressure and send the data in short range (15 cm)



Due to battery life

4 days with total current of 100uA

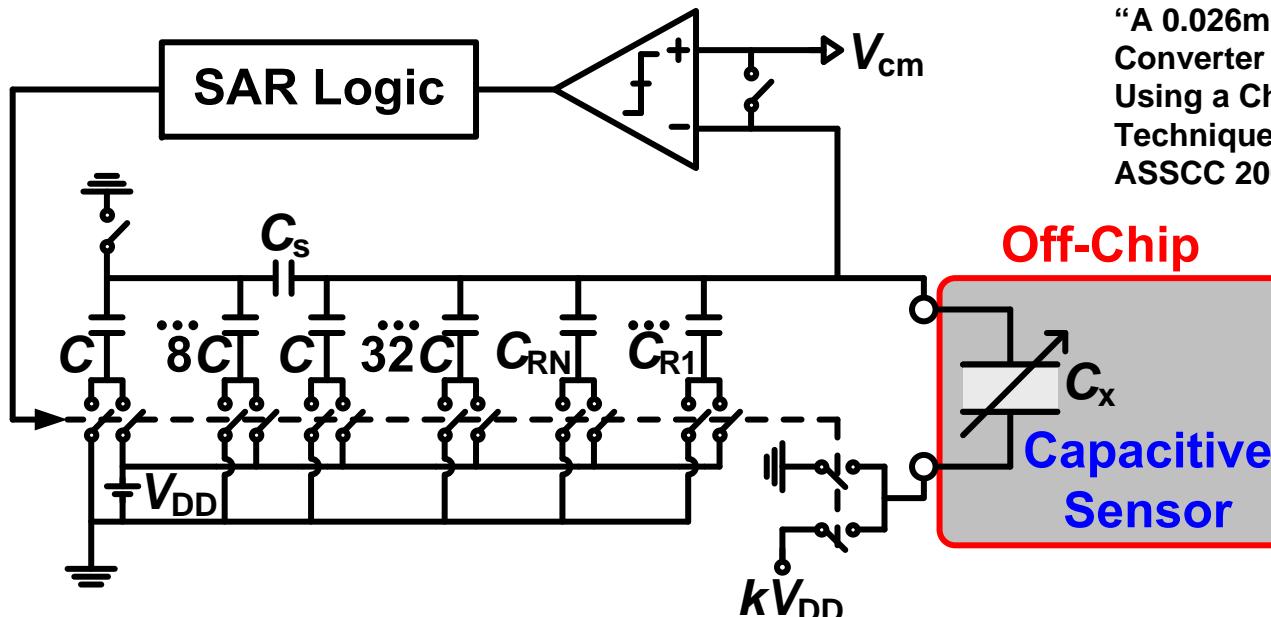
All analog and RF circuits consumes only 30uA

SAR ADC + Capacitive pressure sensor

- Low power
- Can compensate the offset capacitance
- Small area
- Insensitive to operating voltage

Kota Tanaka, Yasuhide Kuramochi,
Takashi Kurashina, Kenichi Okada,
and Akira Matsuzawa

"A 0.026mm² Capacitance-to-Digital
Converter for Biotelemetry Applications
Using a Charge Redistribution
Technique"
ASSCC 2007

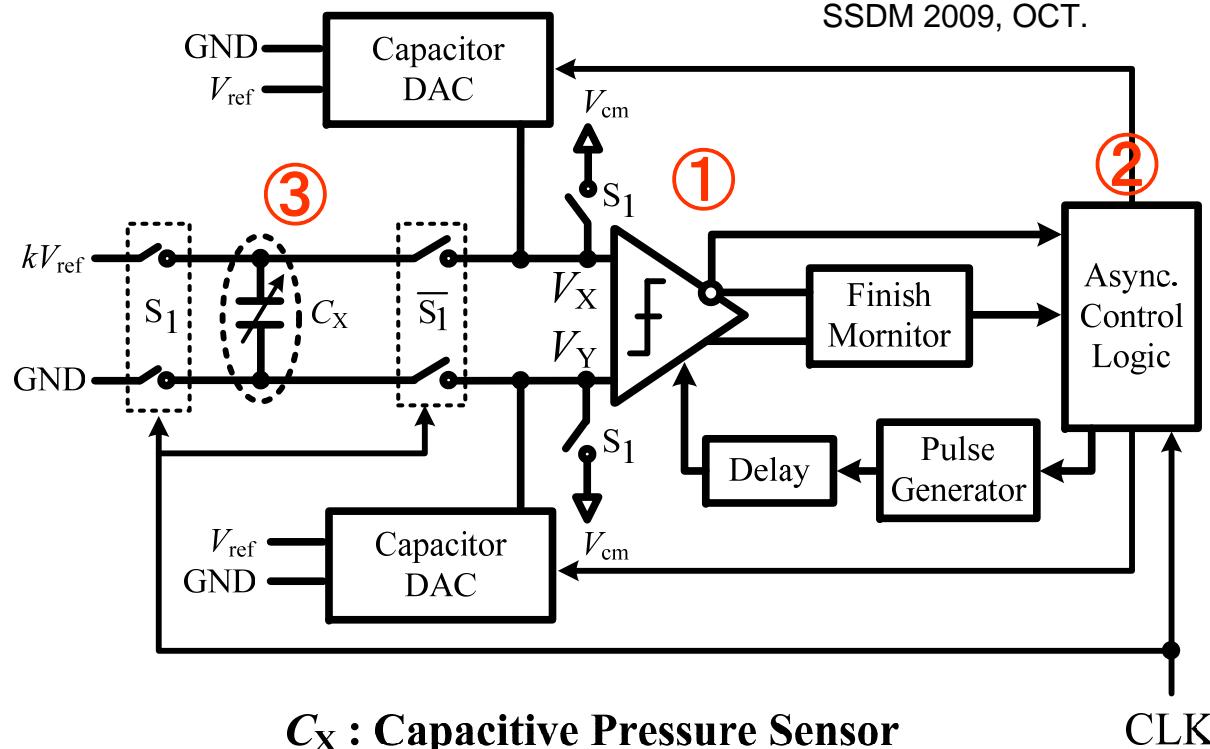


Ultra-low power CDC

Improved Capacitance to Digital Converter.

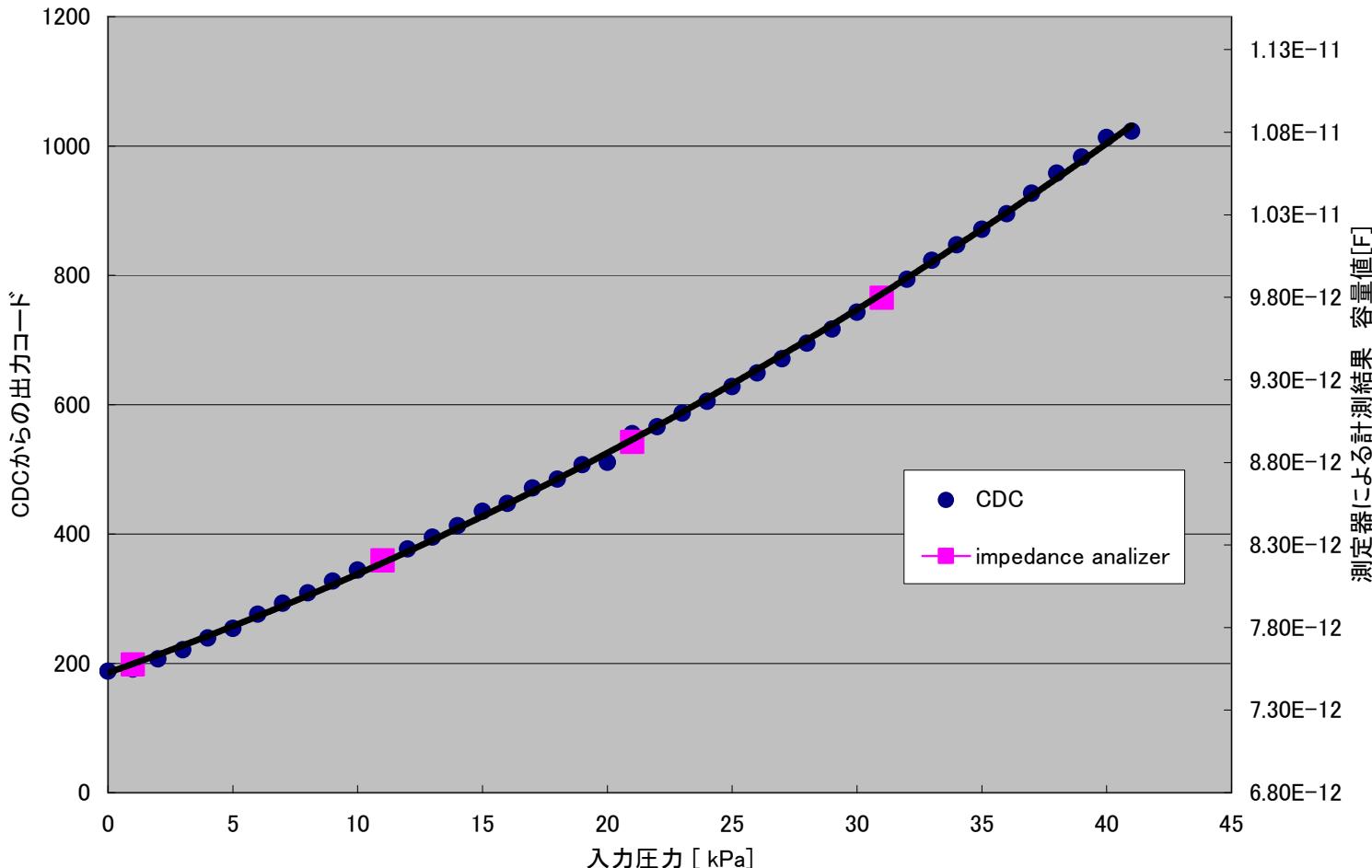
1. 10b SAR like architecture 3nA @ 30 times/sec
2. Self-clocking
3. Single to differential

Tuan Minh Vo, Yasuhide Kuramochi, Masaya Miyahara, Takashi Kurashina, and Akira Matsuzawa
 "A 10-bit, 290 fJ/conv. Steps, 0.13mm², Zero-Static Power, Self-Timed Capacitance to Digital Converter."
 SSDM 2009, OCT.



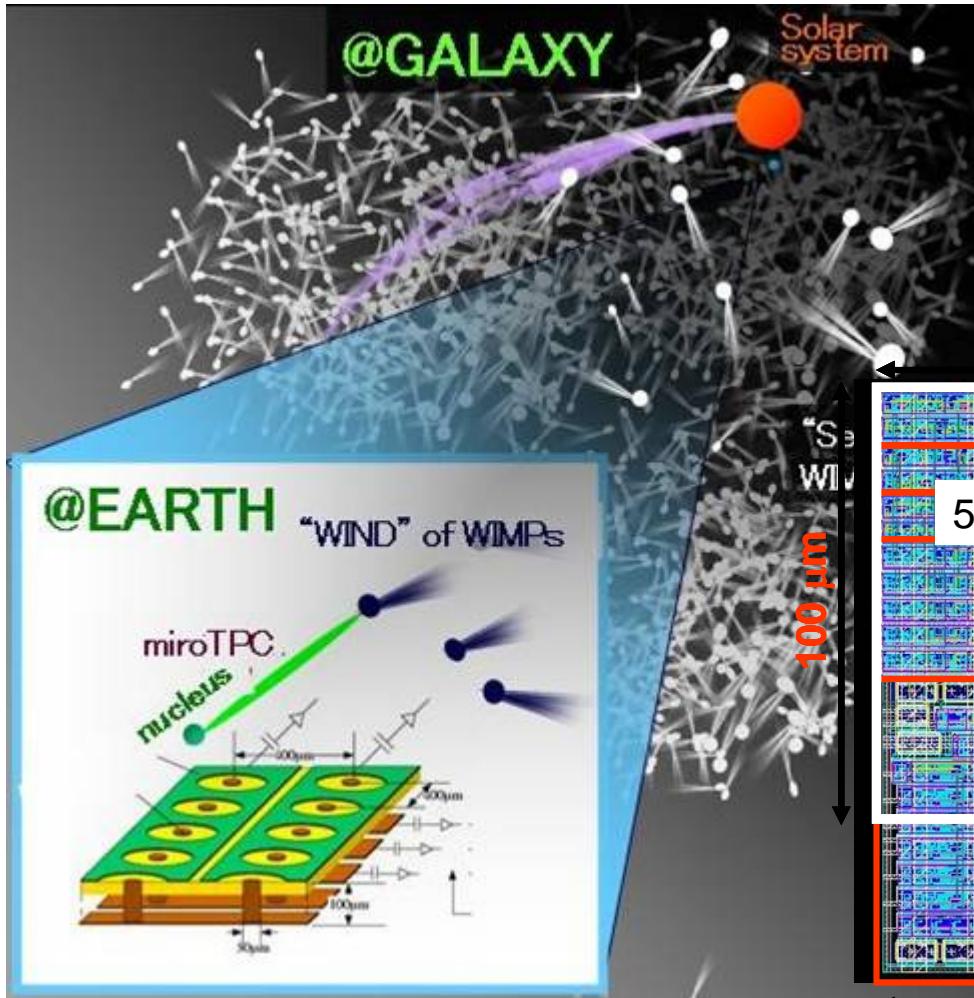
Accuracy

Same accuracy as an impedance meter.

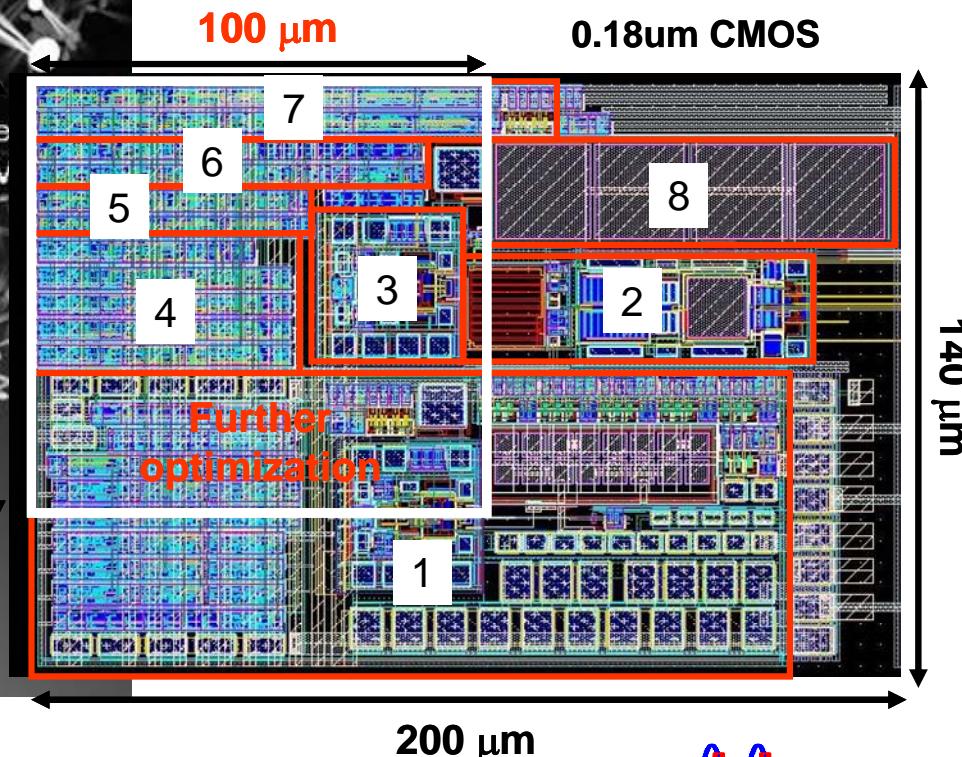


Developing new particle detector for nuclear physics

QPIX



A. Matsuzawa, Vu Minh Khoa, M. Miyahara, T. Kurashina, A. Sugiyama, K. Miuchi, and S. Tanaka, "A new particle detector LSI Qpix: integrating high speed ADC for each pixel", The 1st international conference on Technology and Instrumentation in Particle Physics, March 2009.

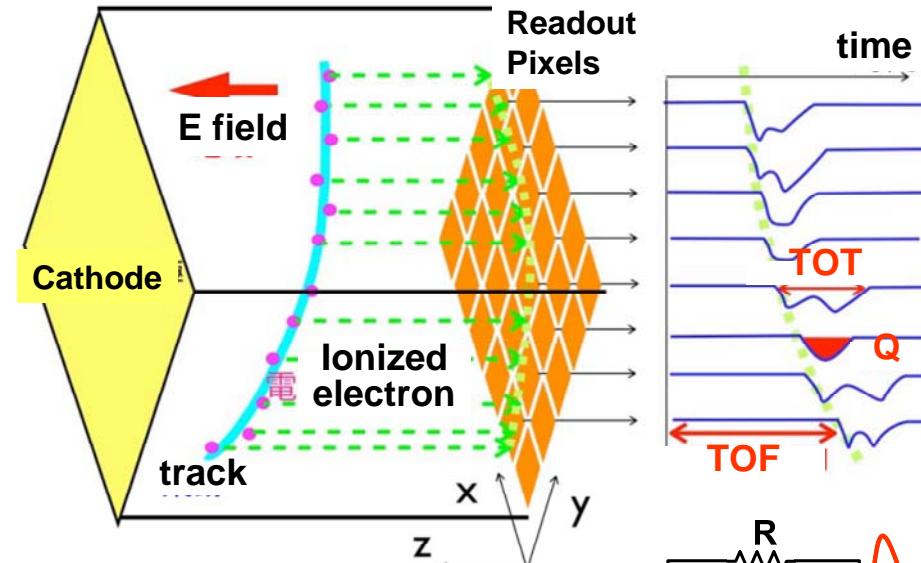


Basic functions of QPIX

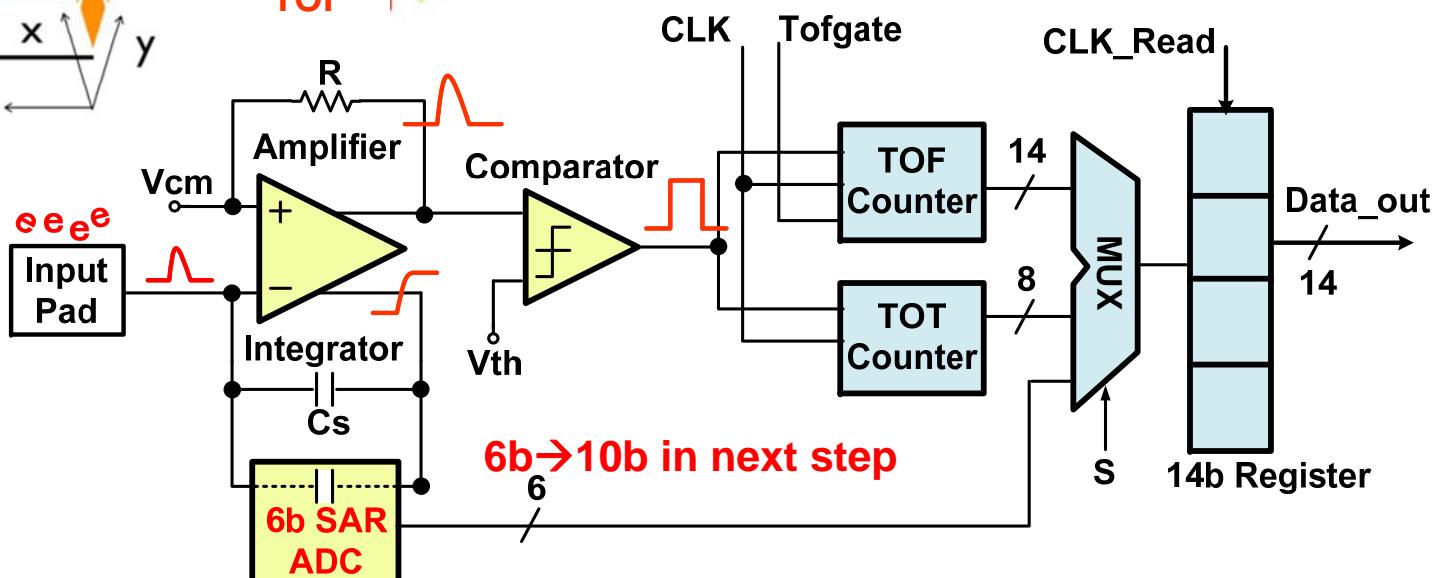
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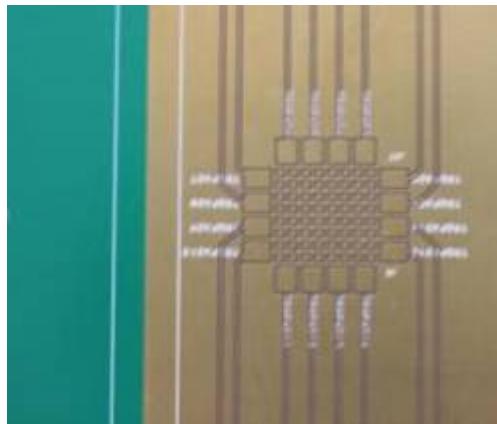
A world first particle detector having an ADC in each pixels.



QPIX can measure the total charge Q , as well as TOF and TOT.

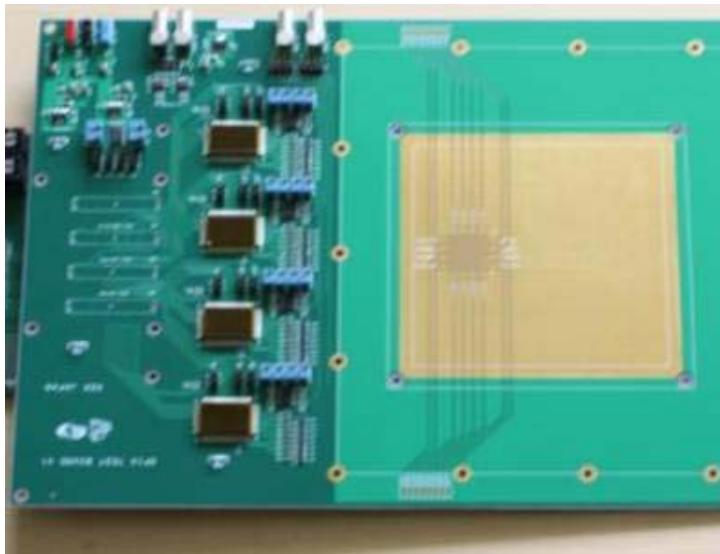


We could detect and measure the nuclear particles

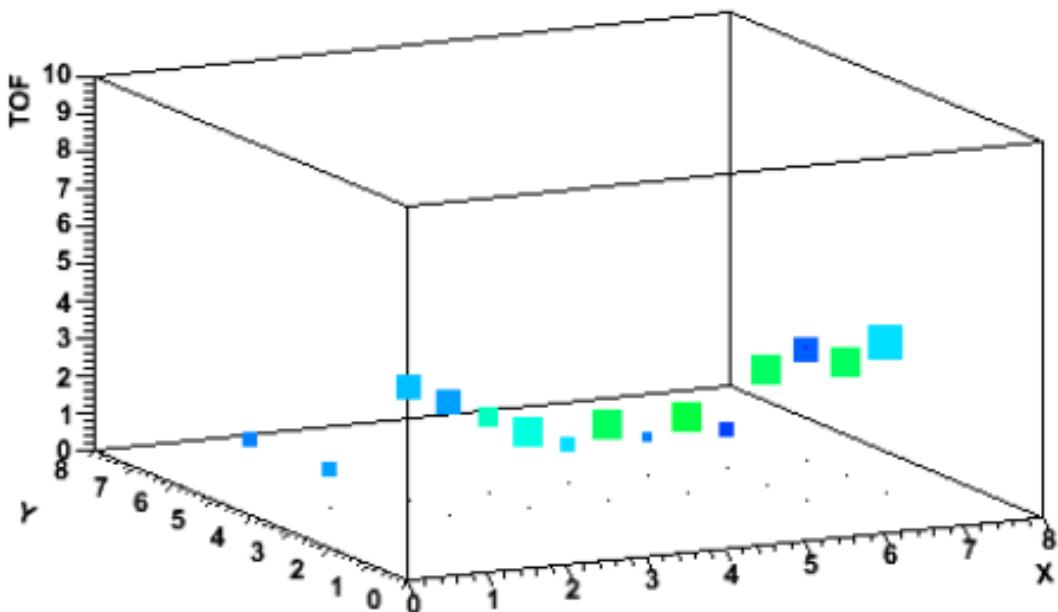


16 pixels

Trajectory of particle



Measuring board



Developed 0.2V LC VCO

Class C with start-up circuit

K. Okada, Y. Nomiyama, R. Murakami, and A. Matsuzawa,
 "A 0.114mW Dual-Conduction Class-C CMOS VCO with 0.2V Power Supply,"
 Dig. Symp. VLSI Circuits, pp.228-229, June, 2009.

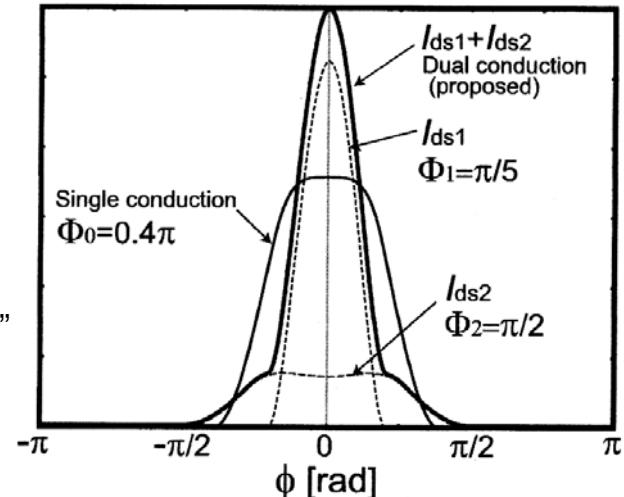
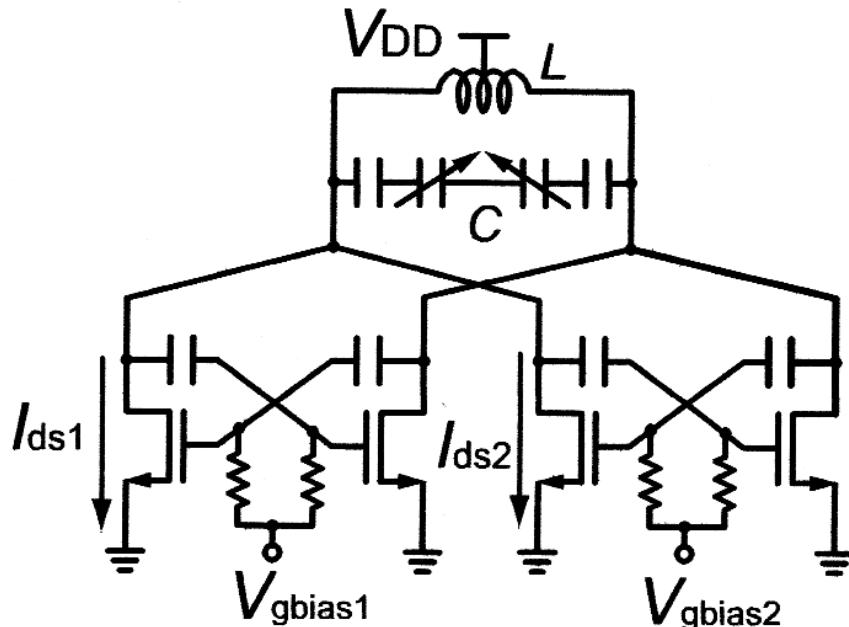


Fig. 2. MOS current waveform of single- and dual-conduction class-C VCOs under the same signal amplitude ($A_t = 3/4 * V_{DD}$, and $V_{th} = 5/2 * V_{DD}$).

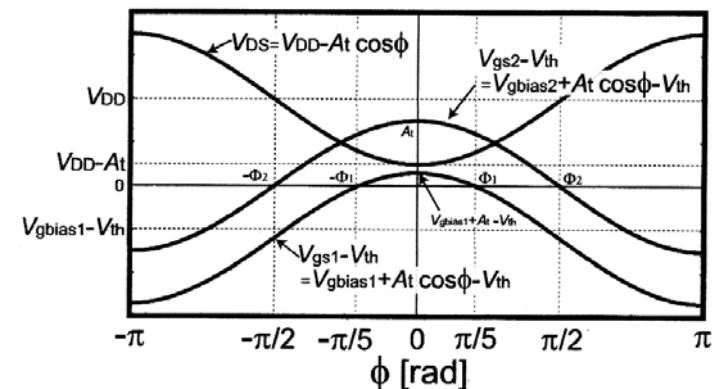


Fig. 3. Voltage waveform of the proposed VCO for drain and both gate voltages.

Performance of 0.2V VCO

33

**Low power of 110uW
at 4.5GHz generation**

**0.2V,
-104dBc/Hz @1MHz-offset
FoM=187dBc/Hz**

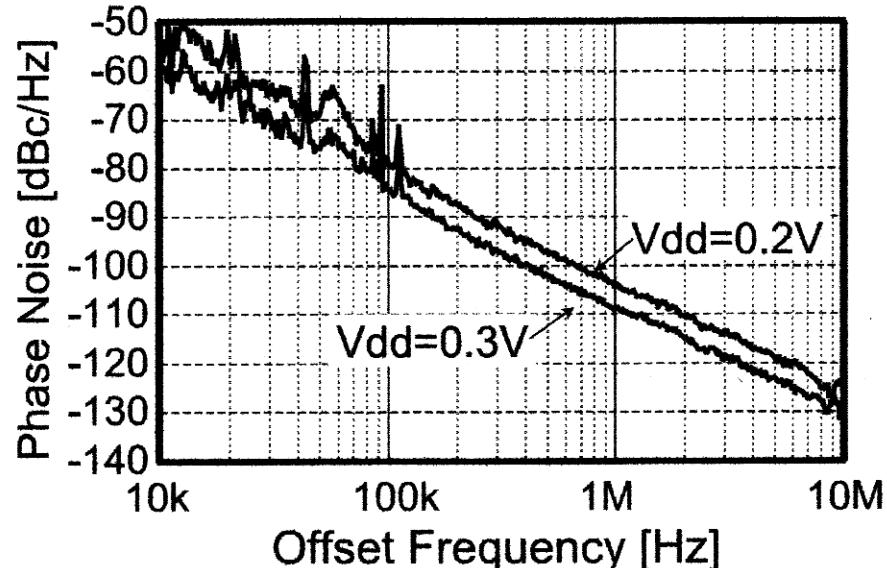


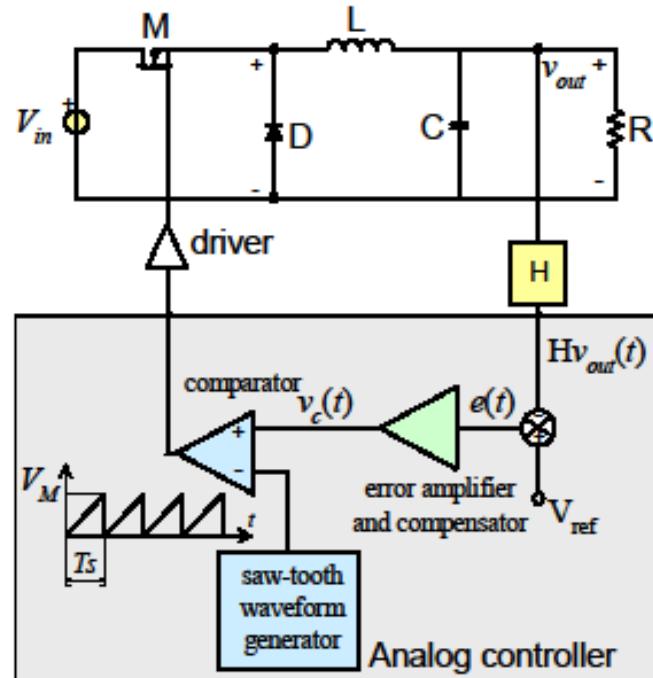
TABLE 1. Performance summary.

	[2]	[1]	[1]	This work	
Technology	0.13 μ m CMOS	0.18 μ m CMOS	0.18 μ m CMOS	0.18 μ m CMOS	
Supply voltage	1.0 V	0.5 V	0.35 V	0.3 V	0.2 V
Power consumption	1.3 mW	0.57 mW	1.46 mW	0.159 mW	0.114 mW
Oscillation frequency	4.9 GHz	3.8 GHz	1.4 GHz	4.5 GHz	4.5 GHz
Phase noise	-130 dBc/Hz @3MHz-offset	-119 dBc/Hz @1MHz-offset	-129 dBc/Hz @1MHz-offset	-109 dBc/Hz @1MHz-offset	-104 dBc/Hz @1MHz-offset
FoM	196 dBc/Hz	193 dBc/Hz	190 dBc/Hz	190 dBc/Hz	187 dBc/Hz
Chip area	0.50 mm ²	0.23 mm ²	0.76 mm ²	0.29 mm ²	
Topology	Class-C (single)	TF	TF	Class-C (dual)	

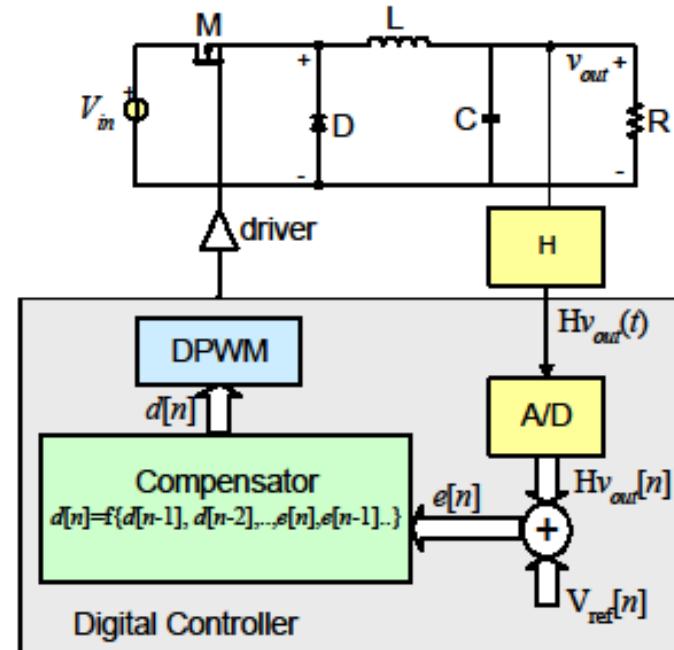
DC/DC converter uses analog control method.

We have started to develop full digital power supply.

Analog Implementation



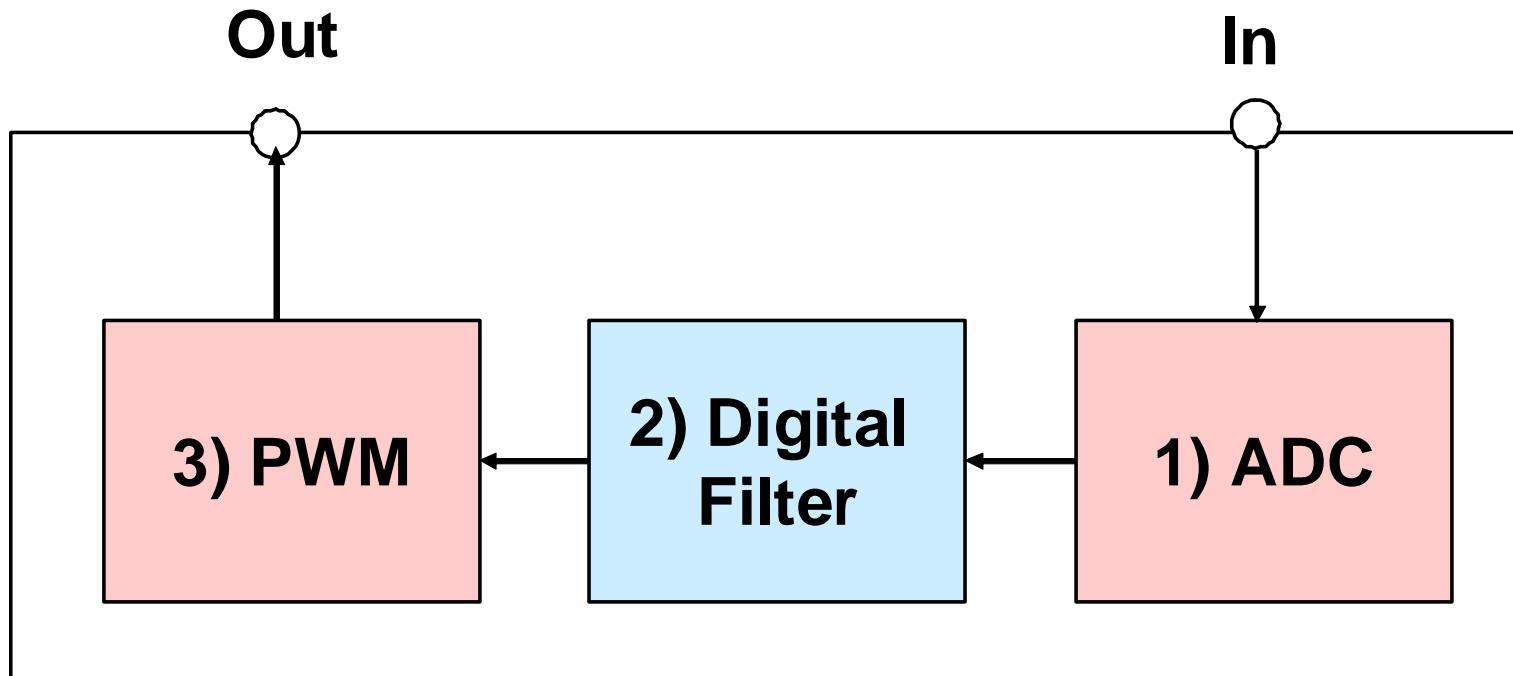
Digital Implementation



We have started to develop ADC and PWM for the first step

ADC: 12bit, 80MSps, 5mW

has low power mode and high speed mode

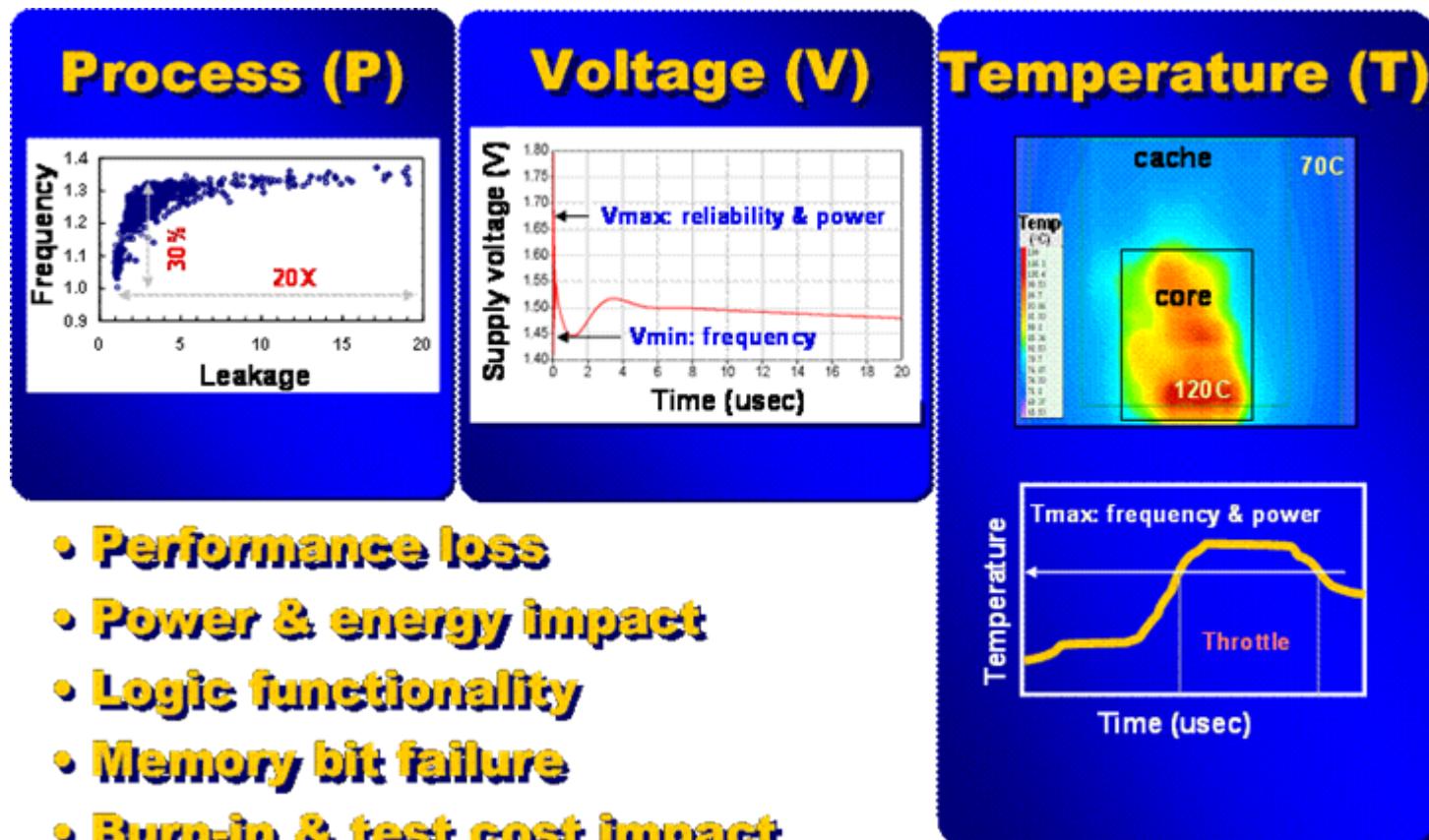


09年に開発開始

10年に開発開始

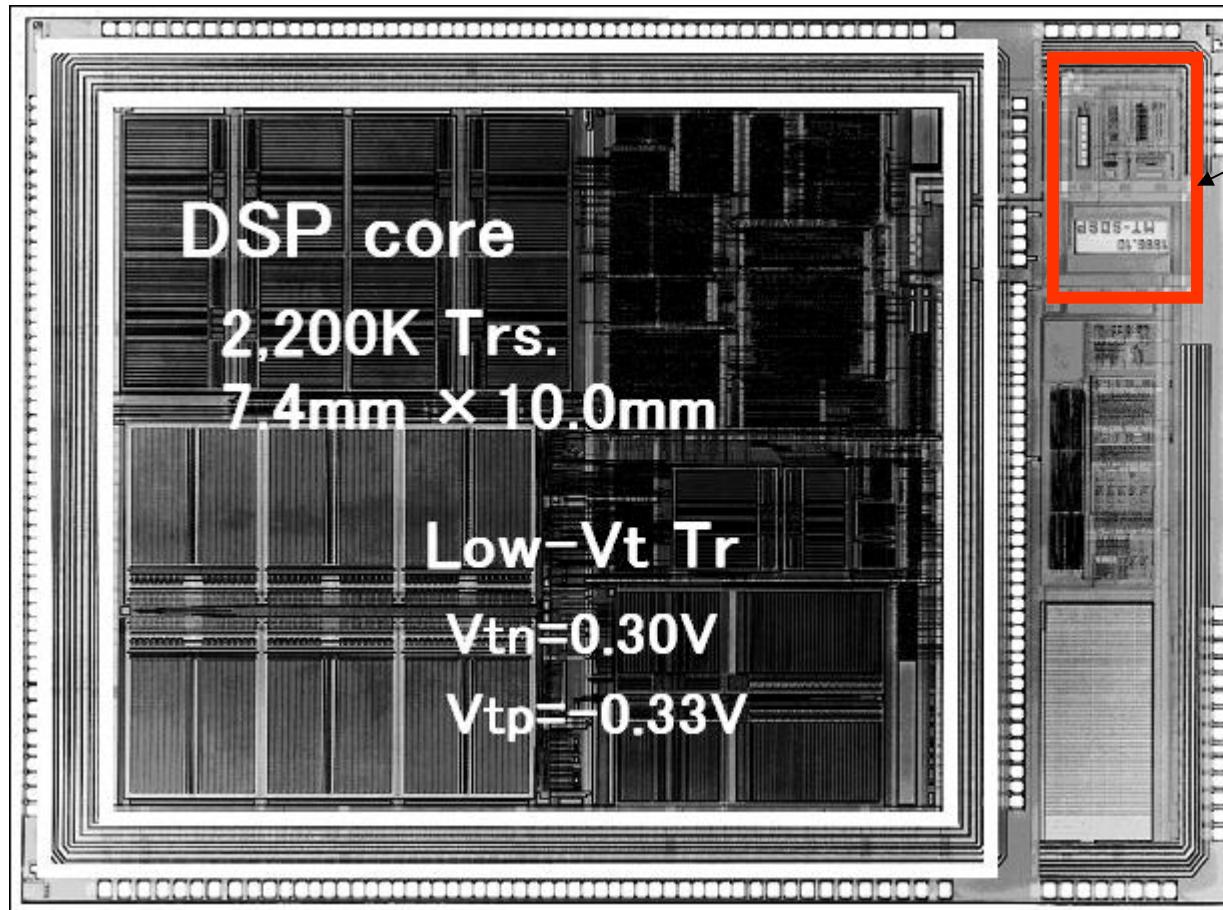
09年に開発開始

Fluctuation of device parameter, stabilization of power supply voltage, and reduction of local heating become serious issues in digital LSIs.



Courtesy
Dr. Vivek De,
Intel

Sakiyama et al., Symp. On VLSI Circuits '97



0.35umCMOS
2.2M Tr
20MIPS
12mW (1.2V, internal)

leak current
500uA: active
1uA: standby

High efficiency of 94% and low noise of 15mVpp.

S.Sakiyama et al., ISSCC99

